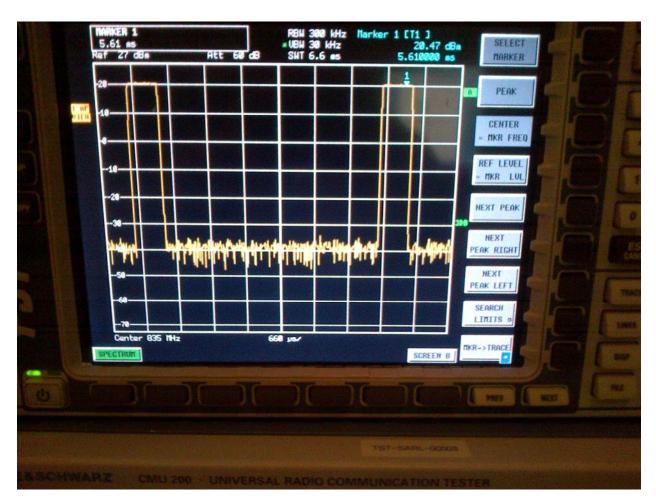
R R R R	ing ices		Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW			
Author Data	Dates of T	est	Report No	FCC ID		
Daoud Attayi		7-29, June 28, 2012)3-04, 2013	RTS-6026-1304-09	L6ARFI	M120LW	

Annex A: Measurement data and plots

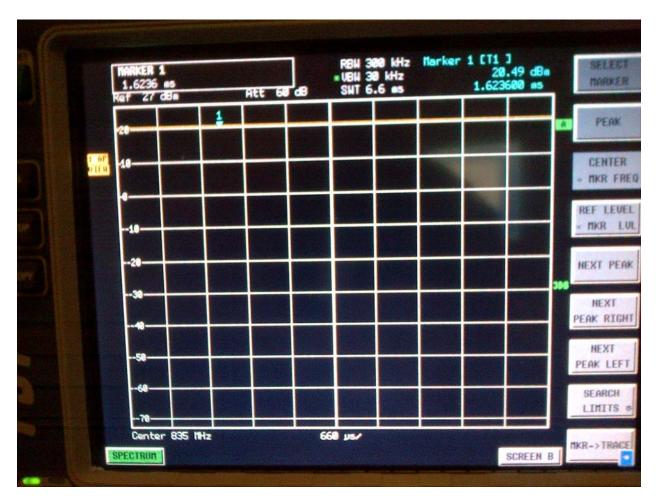
A.1 Spectrum analyser plots: GSM, UMTS, CDMA, CW, 80%AM, signals

	esting ervices		ompatibility RF Emissions T ® Smartphone model RFM12		Page 2 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi Feb. 17-29, June 28, 2012		7-29, June 28, 2012	RTS-6026-1304-09	L6ARF	M120LW
-	April	03-04, 2013			



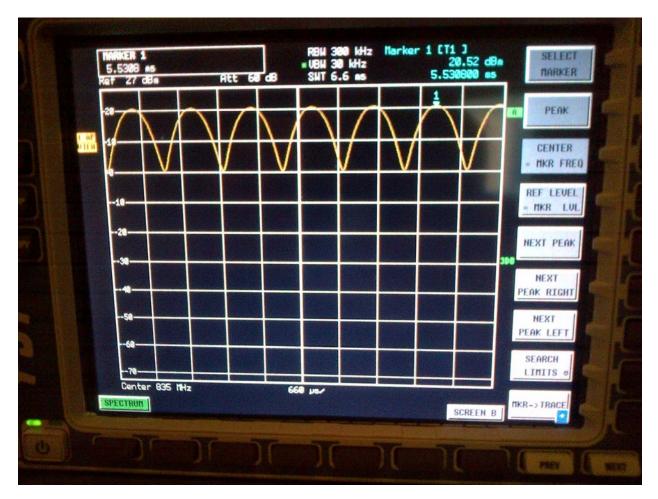
GSM 835 MHz

	Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW				Page 3 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW



CW 835 MHz

Author Data				Page 4 (154)	
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARFI	W120LW



AM 80% 835 MHz

R R R R	ting NCES		Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW			
Author Data	Dates of T	est	Report No	FCC ID		
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW	



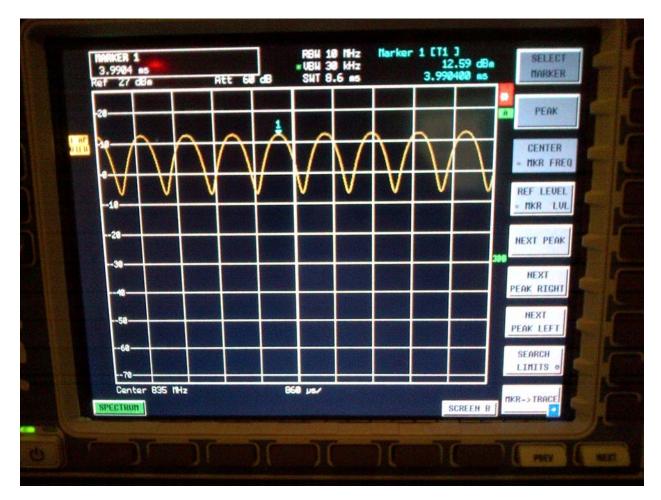
UMTS 835 MHz

Author Data				Page 6 (154)	
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARFN	/120LW



CW 835 MHz

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Daoud Attayi		7-29, June 28, 2012 3-04, 2013	RTS-6026-1304-09	L6ARF	M120LW



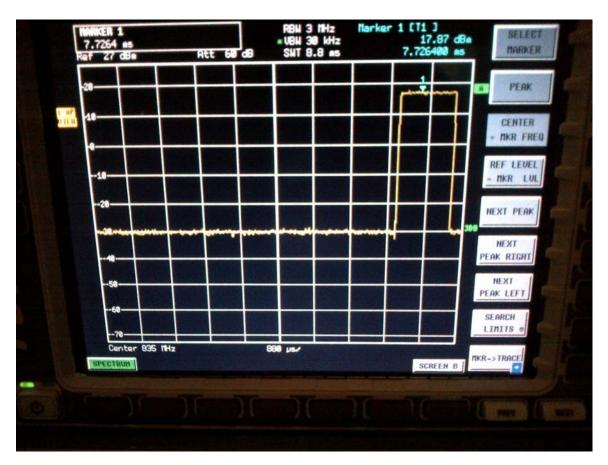
AM 80% 835 MHz

R ate State	Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW				Page 8 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARFI	M120LW



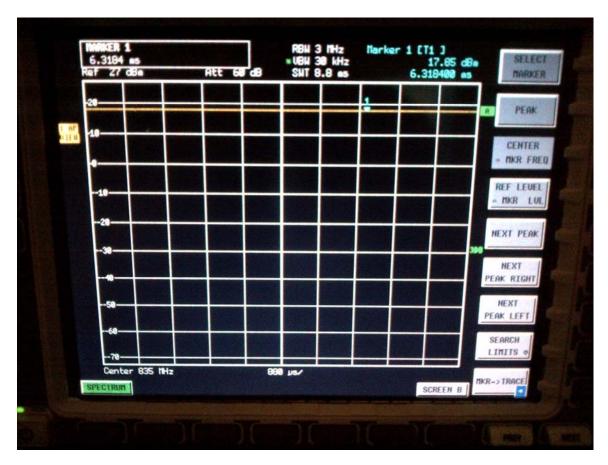
CDMA 835 MHz (BC0)

Document Annex A to Hearing Aid Compatibility RF Emissions Tes Report for the BlackBerry® Smartphone model RFM121L			Page 9 (154)		
Author Data	Dates of T		Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARFI	M120LW



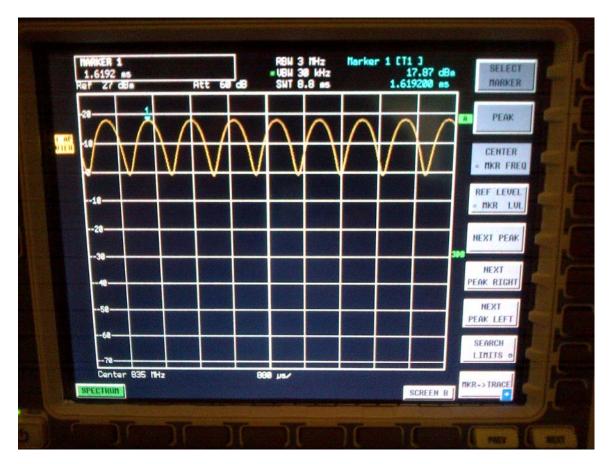
CDMA 835 MHz (BC0) 1/8th

	ting vices:	of Test			
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW



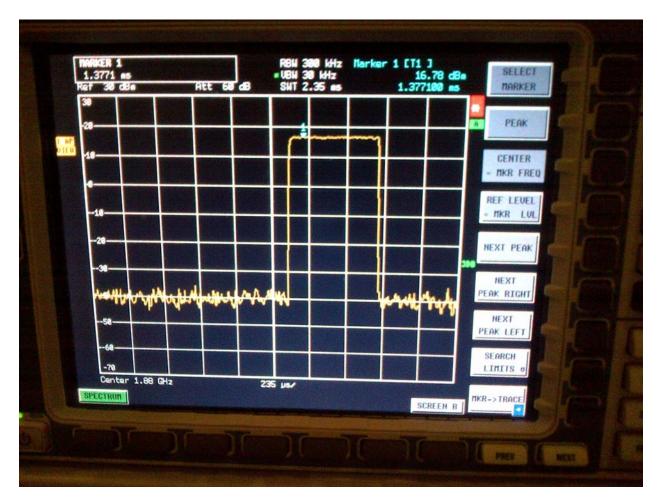
CW 835 MHz

	Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW				Page 11 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW



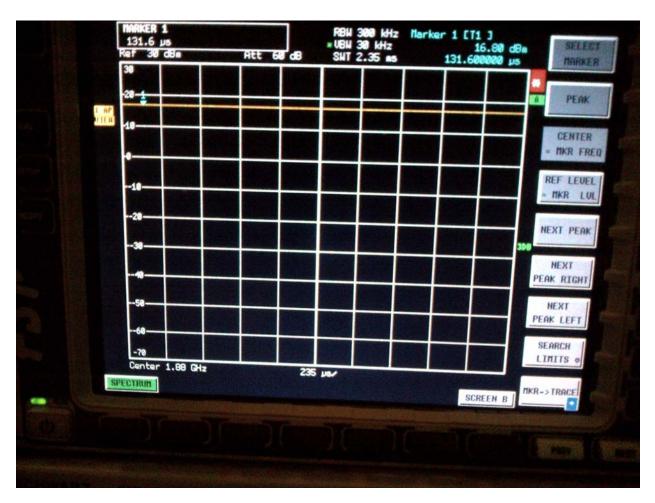
AM 80% 835 MHz

	ting NCES"	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW			
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW



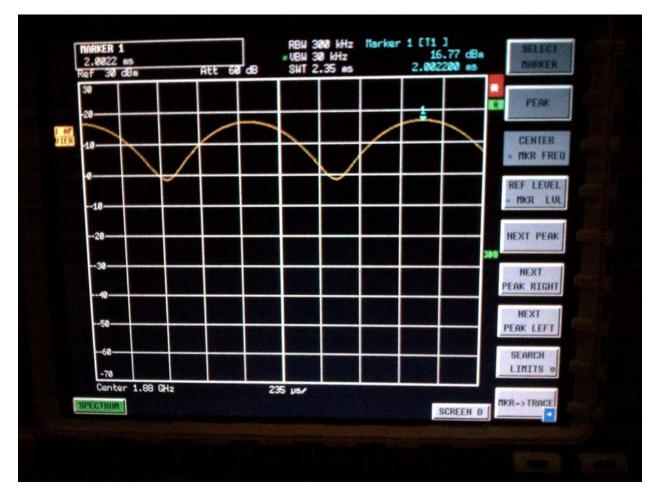
GSM 1880 MHz

• Jestra		Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW			Page 13 (154)
Author Data	Dates of T		Report No	FCC ID	
Daoud Attayi	aoud Attayi Feb. 17-29, June 28, 2012		RTS-6026-1304-09	L6ARF	M120LW
	April	03-04, 2013			



CW 1880 MHz

	ting vices		ompatibility RF Emissions T ® Smartphone model RFM12		Page 14 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi	oud Attayi Feb. 17-29, June 28, 2012 April 03-04, 2013		RTS-6026-1304-09	L6ARFI	M120LW



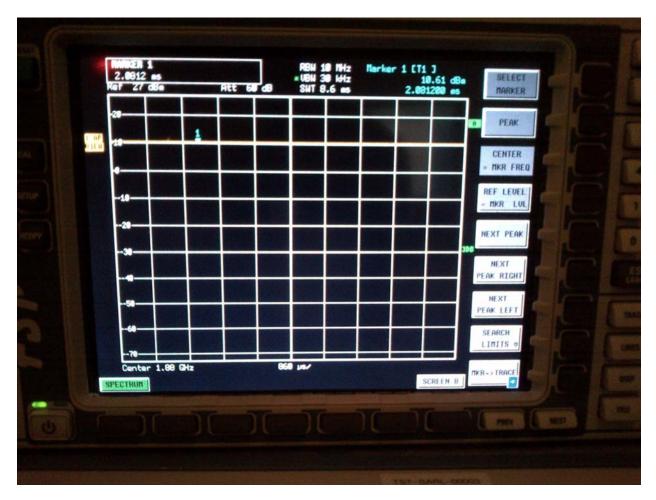
AM 80 % 1880 MHz

		Annex A to Hearing Aid Compat	ex A to Hearing Aid Compatibility RF Emissions Test ort for the BlackBerry® Smartphone model RFM121LW		Page 15 (154)
Author Data	Dates of T		Report No	FCC ID	
Daoud Attayi	Daoud Attayi Feb. 17-29, June 28, 2012		RTS-6026-1304-09	L6ARF	/120LW
	April	03-04, 2013			



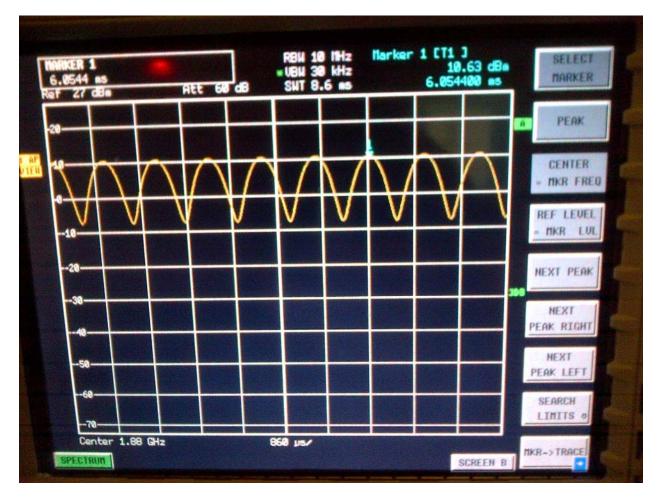
UMTS 1880 MHz

Testing Services		Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW			Page 16 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARFI	M120LW



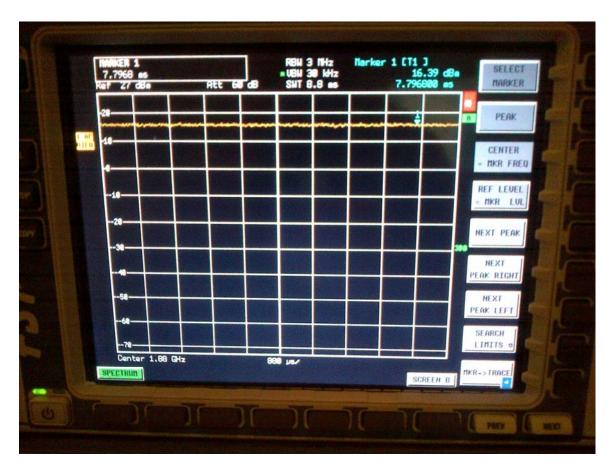
CW 1880 MHz

Partices Services		Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW			Page 17 (154)
Author Data	Dates of T		Report No	FCC ID	
Daoud Attayi Feb. 17-29, June 28, 2012		RTS-6026-1304-09	L6ARF	M120LW	
	April (03-04, 2013			



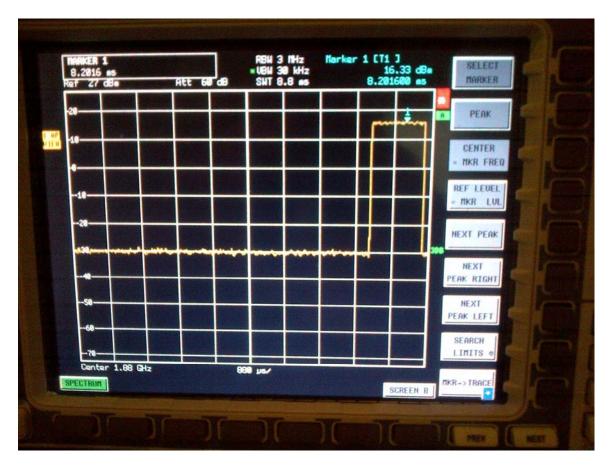
AM 80 % 1880 MHz

	sting rvices"		ompatibility RF Emissions T ® Smartphone model RFM12		Page 18 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW



CDMA 1880 MHz (BC1)

Testing Services"		Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW			Page 19 (154)
Author Data	Dates of T		Report No	FCC ID	
Daoud Attayi	Feb. 17-29, June 28, 2012		RTS-6026-1304-09	L6ARF	M120LW
	April (03-04, 2013			



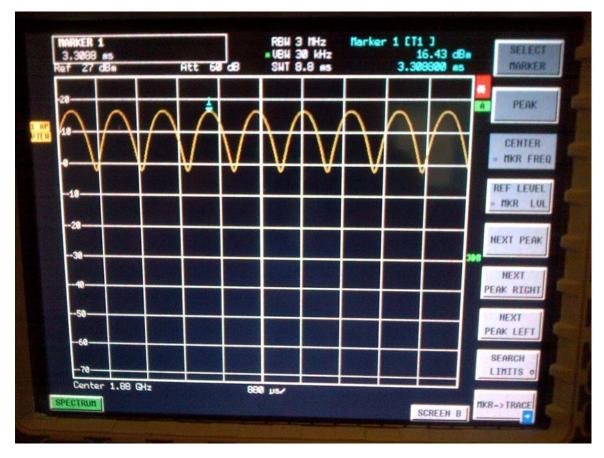
CDMA 1880 MHz (BC1) 1/8 th

		id Compatibility RF Emissions Test erry® Smartphone model RFM121LW		Page 20 (154)	
Author Data	Dates of Tes	st	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 3-04, 2013	RTS-6026-1304-09	L6ARF	M120LW



CW 1880 MHz

Testing Services		Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW			Page 21 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi Feb. 17-29, June 28, 2012 April 03-04, 2013		RTS-6026-1304-09	L6ARF	M120LW	



AM 80% 1880 MHz

R	sting rvices		ompatibility RF Emissions Te Smartphone model RFM12 ⁴		Page 22 (154)
Author Data	Dates of Te	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012)3-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

A.2 Dipole validation and probe modulation factor plots

Part Iesting Services		Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW			Page 23 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012	RTS-6026-1304-09	L6ARF	M120LW
	April	03-04, 2013			

Date/Time: 4/3/2013 3:14:37 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_validation_835 MHz_04_03_13

DUT: HAC-Dipole 835 MHz; Type: CD835V3; Serial: 1011

Communication System: CW; Frequency: 835 MHz Medium parameters used: $\sigma = 0$ S/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 SN2286; ConvF(1, 1, 1); Calibrated: 1/11/2013;
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

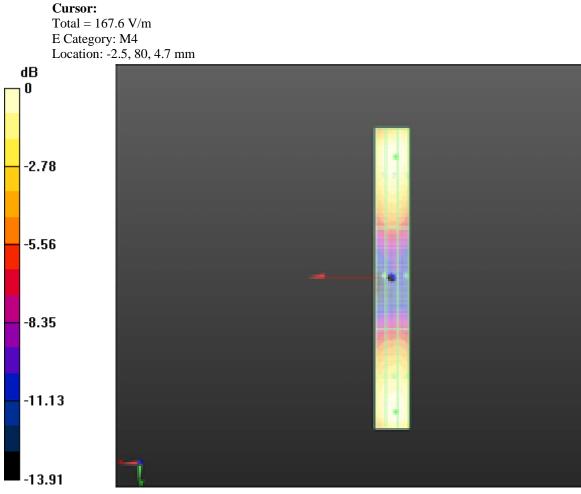
Dipole E-Field measurement/E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test

(41x361x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 106.4 V/m; Power Drift = 0.05 dBPMR not calibrated. PMF = 1.000 is applied. E-field emissions = 167.6 V/mNear-field category: M4 (AWF 0 dB)

PMF scaled E-f	ield	
Grid 1 M4	Grid 2 M4	Grid 3 M4
159.3 V/m	167.1 V/m	166.4 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
85.12 V/m	87.66 V/m	86.00 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4

	ting vices:		ompatibility RF Emissions T ® Smartphone model RFM12		Page 24 (154)
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Daoud Attayi		7-29, June 28, 2012)3-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

154.8 V/m 167.6 V/m 167.2	V/m
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0 dB = 167.6 V/m = 44.49 dBV/m

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Daoud Attayi Feb. 17-29, June 28, 2012		RTS-6026-1304-09	L6ARFN	/120LW	
	April	03-04, 2013			

Date/Time: 6/28/2012 1:13:34 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_PMF_GSM835 MHz_06_28_12

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1011

Communication System: GSM 835_PMF, Communication System: CW, Communication System: AM 80%; Frequency: 835 MHz Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole E-Field measurement/E Scan - GSM 835_PMF/Hearing Aid

Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm Device Reference Point: 0, 0, -6.3 mm

Reference Value = 34.76 V/m; Power Drift = -0.00 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 54.25 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-fi	eld	
Grid 1 M4	Grid 2 ${f M4}$	Grid 3 M4
49.26 V/m	51.48 V/m	51.48 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
27.95 V/m	28.56 V/m	28.13 V/m
Grid 7 M4	Grid 8 ${f M4}$	Grid 9 M4
51.48 V/m	54.25 V/m	53.95 V/m

Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121L				Page 26 (154)	
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012)3-04, 2013	RTS-6026-1304-09	L6ARFI	M120LW

Cursor: Total = 54.247 V/m E Category: M4 Location: -2.5, 80.5, 4.7 mm

Dipole E-Field measurement/E Scan - CW 835_PMF/Hearing Aid

Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 103.0 V/m; Power Drift = -0.02 dB PMR not calibrated. PMF = 1.000 is applied. E-field emissions = 162.8 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
148.5 V/m	160.5 V/m	160.4 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
82.74 V/m	86.24 V/m	84.62 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
158.1 V/m	162.8 V/m	155.2 V/m

Cursor:

Total = 162.8 V/m E Category: M4 Location: 0.5, 79.5, 4.7 mm

Dipole E-Field measurement/E Scan - AM80%_ 835_PMF/Hearing Aid Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm Reference Value = 64.73 V/m; Power Drift = 0.02 dB PMR not calibrated. PMF = 1.000 is applied. E-field emissions = 102.0 V/m

Near-field category: M4 (AWF 0 dB)

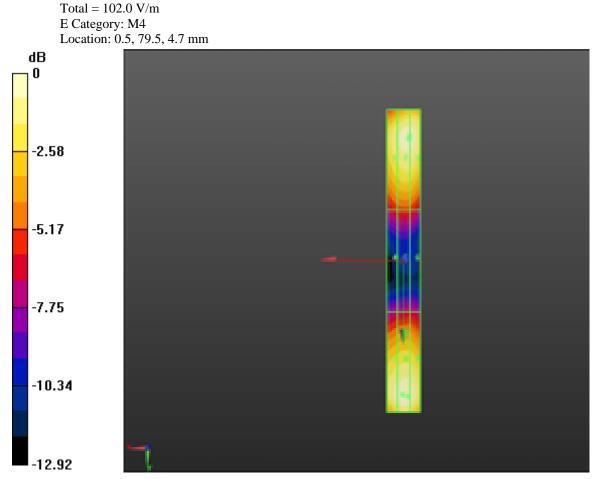
PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
93.30 V/m	100.3 V/m	100.3 V/m
Grid 4 ${f M4}$	Grid 5 M4	Grid 6 ${f M4}$

R R R R	ting NCES"		ompatibility RF Emissions Te ® Smartphone model RFM121		Page 27 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARFI	M120LW

52.75 V/m	54.62 V/m	53.83 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
99.38 V/m	102.0 V/m	97.92 V/m





0 dB = 54.250 V/m = 34.69 dB V/m

		ompatibility RF Emissions T ® Smartphone model RFM12		Page 28 (154)	
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

Date/Time: 2/17/2012 12:24:15 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_PMF_UMTS835 MHz_02_17_12

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1011

Communication System: WCDMA FDD V, Communication System: CW, Communication System: AM 80%; Frequency: 835 MHz Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn472; Calibrated: 3/7/2011
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole E-Field measurement/E Scan - UMTS 835_PMF/Hearing Aid Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 41.08 V/m; Power Drift = 0.03 dB PMR not calibrated. PMF = 1.000 is applied. E-field emissions = 64.41 V/m Near-field category: M4 (AWF 0 dB)

	sting vices		ompatibility RF Emissions ® Smartphone model RFM1		Page 29 (154)
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Daoud Attayi		7-29, June 28, 2012 03-04. 2013	RTS-6026-1304-09	LOARF	M120LW

PMF scaled E-f	ield	
Grid 1 M4	Grid 2 M4	Grid 3 M4
53.11 V/m	55.59 V/m	55.40 V/m
Grid 4 M4	Grid 5 M4	Grid 6 ${f M4}$
29.72 V/m	30.66 V/m	29.79 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
61.55 V/m	64.41 V/m	63.22 V/m

Cursor:

Total = 64.412 V/m E Category: M4 Location: -0.5, 79, 4.7 mm

Dipole E-Field measurement/E Scan - CW 835_PMF/Hearing Aid Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm Reference Value = 43.11 V/m; Power Drift = -0.14 dB PMR not calibrated. PMF = 1.000 is applied. E-field emissions = 68.64 V/m

Near-field category: M4 (AWF 0 dB)

 PMF scaled E-f	ield	
Grid 1 ${f M4}$	Grid 2 $\mathbf{M4}$	Grid 3 M4
58.55 V/m	59.20 V/m	57.13 V/m
Grid 4 ${f M4}$	Grid 5 M4	Grid 6 M4
32.35 V/m	32.63 V/m	31.24 V/m
Grid 7 ${f M4}$	Grid 8 M4	Grid 9 M4
61.85 V/m	68.64 V/m	68.56 V/m

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Daoud Attayi Feb. 17-29, June 28, 2012 April 03-04, 2013		RTS-6026-1304-09	L6ARF	M120LW	

Cursor: Total = 68.635 V/m E Category: M4 Location: -3, 79.5, 4.7 mm

Dipole E-Field measurement/E Scan - AM80%_ 835_PMF/Hearing Aid Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm Reference Value = 28.41 V/m; Power Drift = 0.09 dB PMR not calibrated. PMF = 1.000 is applied. E-field emissions = 45.21 V/m

Near-field category: M4 (AWF 0 dB)

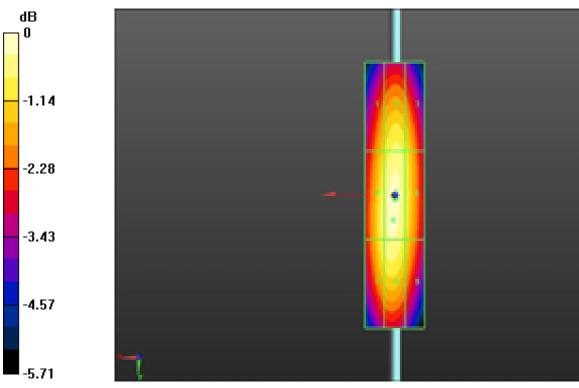
PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
38.28 V/m	38.73 V/m	37.25 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
21.72 V/m	21.89 V/m	20.80 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
40.90 V/m	45.21 V/m	45.16 V/m

Cursor:

Total = 45.209 V/m E Category: M4 Location: -3, 79.5, 4.7 mm

Part Testing Services			ompatibility RF Emissions To Smartphone model RFM12		Page 31 (154)
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0 dB = 0.180 A/m = -14.89 dB A/m

Performances Services			ompatibility RF Emissions Te Smartphone model RFM12		Page 32 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi Feb. 17-29, June 28, 2012 April 03-04, 2013		RTS-6026-1304-09	L6ARF	M120LW	

Test Laboratory: RIM Testing Services

HAC RF_E-Field_PMF_CDMA835 MHz_02_29_12

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1011

Communication System: CDMA 850, Communication System: CDMA 850 1/8th,

Communication System: CW, Communication System: AM 80%; Frequency: 835 MHz

Medium parameters used: σ = 0 mho/m, ϵ_r = 1; ρ = 0 kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole E-Field measurement/E Scan - CDMA FR 835_PMF/Hearing Aid

Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 79.95 V/m; Power Drift = -0.18 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 118.9 V/m

Near-field category: M4 (AWF 0 dB)

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PMF scaled E-field

Grid 1 M4 104.7 V/m	Grid 2 M4 108.7 V/m	
Grid 4 M4 56.56 V/m		
Grid 7 M4 112.0 V/m	Grid 8 M4 118.9 V/m	

Cursor:

Total = 118.9 V/m E Category: M4 Location: -0.5, 79, 4.7 mm

Dipole E-Field measurement/E Scan - CDMA 1/8th 835_PMF 2/Hearing Aid

Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 30.10 V/m; Power Drift = 0.23 dB PMR not calibrated. PMF = 1.000 is applied. E-field emissions = 43.21 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
39.00 V/m	41.81 V/m	39.31 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
20.47 V/m	22.99 V/m	20.34 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
41.05 V/m	43.21 V/m	42.62 V/m

Annex			ompatibility RF Emissions T ® Smartphone model RFM12		Page 34 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi Feb. 17-29, June 28, 2012 April 03-04, 2013			RTS-6026-1304-09	L6ARF	M120LW

Cursor: Total = 43.214 V/m E Category: M4 Location: -0.5, 84, 4.7 mm

Dipole E-Field measurement/E Scan - CW 835_PMF/Hearing Aid Compatibility

Test (41x361x1): Measurement grid: dx=5mm, dy=5mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 82.56 V/m; Power Drift = -0.07 dB PMR not calibrated. PMF = 1.000 is applied. E-field emissions = 125.5 V/m Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4 110.7 V/m	
Grid 4 M4 60.24 V/m	
Grid 7 M4 119.5 V/m	

Cursor:

Total = 125.5 V/m E Category: M4 Location: -0.5, 79, 4.7 mm

Dipole E-Field measurement/E Scan - AM80%_ 835_PMF/Hearing Aid

Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 51.22 V/m; Power Drift = 0.06 dB PMR not calibrated. PMF = 1.000 is applied. E-field emissions = 78.06 V/m

Near-field category: M4 (AWF 0 dB)

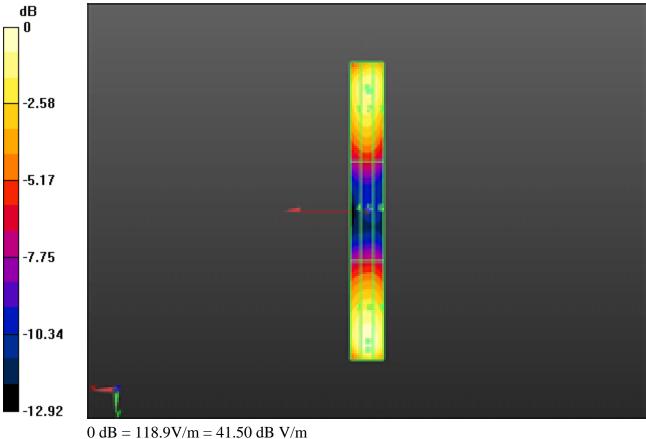
		Document Annex A to Hearing Aid Com Report for the BlackBerry® S			Page 35 (154)
Author Data Dates of T		est	Report No	FCC ID	
Daoud Attayi Feb. 17-29, June 28, 2012 April 03-04, 2013		RTS-6026-1304-09	L6ARFI	W120LW	

PMF scaled E-field

Grid 1 M4 69.60 V/m	
Grid 4 M4 38.16 V/m	
Grid 7 M4 74.44 V/m	

Cursor:

Total = 78.060 V/m E Category: M4 Location: -0.5, 79, 4.7 mm



	esting ervices		ompatibility RF Emissions [®] Smartphone model RFM1		Page 36 (154)
Author Data	a Dates of Test		Report No	FCC ID	
Daoud Attayi	bud Attayi Feb. 17-29, June 28, 2012 April 03-04, 2013		RTS-6026-1304-09	L6ARFM120LW	

Date/Time: 4/3/2013 3:42:14 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_validation_1880 MHz_04_03_13

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: CW; Frequency: 1880 MHz Medium parameters used: $\sigma = 0$ S/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 SN2286; ConvF(1, 1, 1); Calibrated: 1/11/2013;
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Dipole E-Field measurement/E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test

(41x181x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm

.

Reference Value = 141.6 V/m; Power Drift = -0.00 dB

PMR not calibrated. PMF = 1.000 is applied.

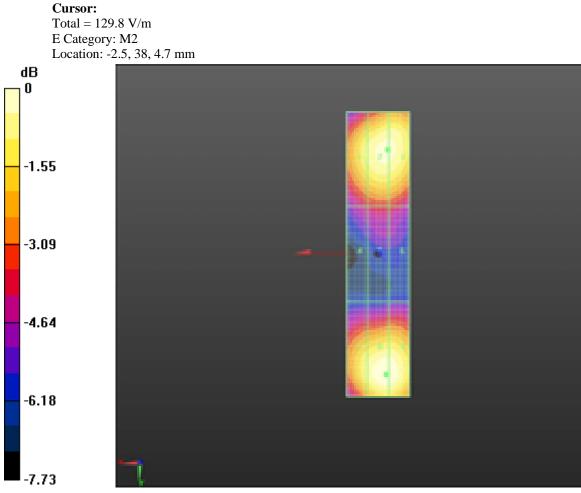
E-field emissions = 129.8 V/m

Near-field category: M2 (AWF 0 dB)

PMF sca	lled E-field		
Grid 1	M2	Grid 2 M2	Grid 3 M2
117.1	V/m	125.5 V/m	125.4 V/m
Grid 4 I	МЗ	Grid 5 M3	Grid 6 M3
82.24	V/m	86.18 V/m	85.16 V/m
Grid 7 I	M2	Grid 8 M2	Grid 9 M2

	ësting ervices"		ompatibility RF Emissions T ® Smartphone model RFM12		Page 37 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARFI	M120LW

117.9 V/m	129.8 V/m	129.4 V/m
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0 dB = 129.8 V/m = 42.27 dBV/m

	ting vices"	Document Annex A to Hearing Aid Compati Report for the BlackBerry® Small			Page 38 (154)
Author Data	Dates of T		Report No	FCC ID	
Daoud Attayi	Feb. 1	7-29, June 28, 2012	RTS-6026-1304-09	L6ARF	/120LW
	April	03-04, 2013			

Date/Time: 6/28/2012 12:54:33 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_PMF_GSM1880 MHz_06_28_12

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: GSM 1880, Communication System: CW, Communication System: AM 80%; Frequency: 1880 MHz Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole E-Field measurement/E Scan - GSM 1880_PMF/Hearing Aid

Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm Reference Value = 33.26 V/m; Power Drift = 0.00 dB PMR not calibrated. PMF = 1.000 is applied. E-field emissions = 29.81 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-fi	ield	
Grid 1 M4	Grid 2 M4	Grid 3 M4
27.34 V/m	28.65 V/m	28.59 V/m
Grid 4 M4	Grid 5 M4	Grid 6 ${f M4}$
19.83 V/m	20.51 V/m	20.10 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
28.20 V/m	29.81 V/m	29.37 V/m

	ting NCES"	Document Annex A to Hearing Aid Con Report for the BlackBerry®			Page 39 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012)3-04, 2013	RTS-6026-1304-09	L6ARFI	W120LW

Cursor: Total = 29.810 V/m E Category: M4 Location: -1, 38.5, 4.7 mm

Dipole E-Field measurement/E Scan- CW 1800_PMF/Hearing Aid

Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 95.34 V/m; Power Drift = 0.01 dB PMR not calibrated. PMF = 1.000 is applied. E-field emissions = 84.88 V/m

Near-field category: M3 (AWF 0 dB)

PMF scaled E-field

Grid 1 M3	Grid 2 M3	Grid 3 M3
78.80 V/m	82.95 V/m	82.43 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
56.84 V/m	58.53 V/m	56.53 V/m
Grid 7 M3	Grid 8 M3	Grid 9 M3
80.11 V/m	84.88 V/m	83.31 V/m

Cursor:

Total = 84.885 V/m E Category: M3 Location: -0.5, 38.5, 4.7 mm

Dipole E-Field measurement/E Scan - AM80%_ 1880_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm Reference Value = 60.62 V/m; Power Drift = -0.03 dB PMR not calibrated. PMF = 1.000 is applied. E-field emissions = 53.60 V/m

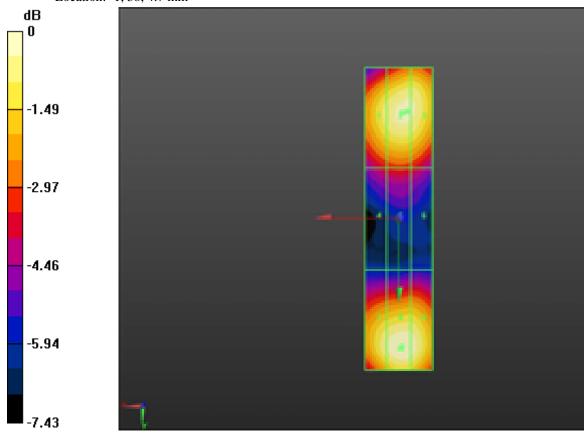
Near-field category: M4 (AWF 0 dB)

	esting rvices		Compatibility RF Emissions T r® Smartphone model RFM12		Page 40 (154)
Author Data	Dates of T		Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012	RTS-6026-1304-09	L6ARF	M120LW
	April	03-04. 2013			

PMF scaled E-f	ield	
Grid 1 M4	Grid 2 $M4$	Grid 3 M4
49.75 V/m	52.55 V/m	52.06 V/m
Grid 4 M4	Grid 5 M4	Grid 6 ${f M4}$
35.78 V/m	36.92 V/m	36.02 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
50.66 V/m	53.60 V/m	52.63 V/m

Cursor:

Total = 53.599 V/m E Category: M4 Location: -1, 38, 4.7 mm



 $0 \ dB = 29.810 V/m = 29.49 \ dB \ V/m$

	êsting ervices		ompatibility RF Emissions T ® Smartphone model RFM12		Page 41 (154)
Author Data	Dates of T	est	Report No	FCC ID	
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	April	03-04, 2013			

Date/Time: 2/17/2012 2:20:23 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_PMF_UMTS1880 MHz_02_17_12

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: WCDMA FDD II, Communication System: CW, Communication System: AM 80%; Frequency: 1880 MHz Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn472; Calibrated: 3/7/2011
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole E-Field measurement/E Scan - UMTS 1880_PMF/Hearing Aid

Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 47.02 V/m; Power Drift = 0.01 dB PMR not calibrated. PMF = 1.000 is applied. E-field emissions = 42.43 V/m Near-field category: M4 (AWF 0 dB)

	sting vices		Compatibility RF Emissions 1		Page 42 (154)
Author Data Daoud Attayi	Dates of T	^{est} 7-29, June 28, 2012	Report No RTS-6026-1304-09	FCC ID	M120LW
Duoud Allayi		03-04. 2013		LUAN	

PMF scaled E-f	ield	
Grid 1 M4	Grid 2 M4	Grid 3 M4
37.98 V/m	39.42 V/m	39.04 V/m
Grid 4 M4	Grid 5 M4	Grid 6 ${f M4}$
26.86 V/m	27.50 V/m	26.70 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
39.63 V/m	42.43 V/m	41.87 V/m

Cursor:

Total = 42.427 V/m E Category: M4 Location: -1, 38, 4.7 mm

Dipole E-Field measurement/E Scan- CW 1800_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm Reference Value = 47.33 V/m; Power Drift = -0.05 dB PMR not calibrated. PMF = 1.000 is applied. E-field emissions = 42.41 V/m

Near-field category: M4 (AWF 0 dB)

PMF sca	led E-field		
Grid 1 I	M 4	Grid 2 M4	Grid 3 ${f M4}$
38.23	V/m	39.51 V/m	39.41 V/m
Grid 4 I	M 4	Grid 5 M4	Grid 6 ${f M4}$
26.94	V/m	27.41 V/m	26.77 V/m
Grid 7 I	M 4	Grid 8 ${f M4}$	Grid 9 M4
40.02	V/m	42.41 V/m	41.99 V/m

PH &	ting lices"	Document Annex A to Hearing Aid Cor Report for the BlackBerry®			Page 43 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012)3-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

Cursor: Total = 42.409 V/m E Category: M4 Location: -1.5, 38, 4.7 mm

Dipole E-Field measurement/E Scan - AM80%_ 1880_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm Reference Value = 30.18 V/m; Power Drift = 0.06 dB

PMR not calibrated. PMF = 1.000 is applied. E-field emissions = 27.40 V/m

Near-field category: M4 (AWF 0 dB)

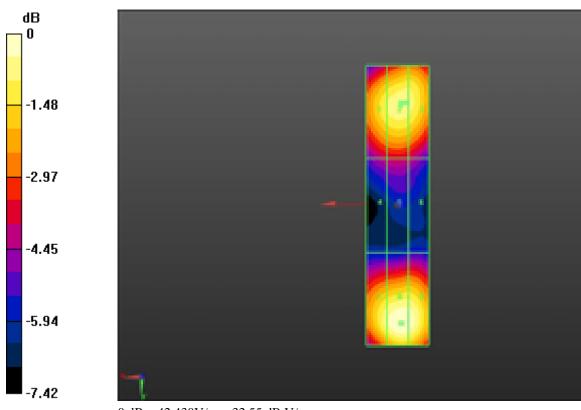
PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
24.40 V/m	25.26 V/m	24.95 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
17.20 V/m	17.65 V/m	17.12 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
25.54 V/m	27.40 V/m	27.02 V/m

Cursor:

Total = 27.402 V/m E Category: M4 Location: -1, 38, 4.7 mm

	ting NCES"	Document Annex A to Hearing Aid Compati Report for the BlackBerry® Smai			Page 44 (154)
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	April (03-04, 2013			



 $0 \ dB = 42.430 V/m = 32.55 \ dB \ V/m$

P#78	ing NCSS		ompatibility RF Emissions Te ® Smartphone model RFM12 ⁴		Page 45 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012)3-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

Test Laboratory: RIM Testing Services

HAC RF_E-Field_PMF_CDMA1880 MHz_02_29_12

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: CDMA 1900, Communication System: CDMA 1900 1/8th,

Communication System: CW, Communication System: AM 80%; Frequency: 1880 MHz

Medium parameters used: σ = 0 mho/m, ϵ_r = 1; ρ = 0 kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole E-Field measurement/E Scan - CDMA FR 1880_PMF/Hearing Aid

Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 87.80 V/m; Power Drift = 0.04 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 80.60 V/m

Near-field category: M3 (AWF 0 dB)

科學	ting vices:		ompatibility RF Emissions To ® Smartphone model RFM12		Page 46 (154)
Author Data	Dates of T		Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

PMF scaled E-field

Grid 1 M3 73.45 V/m	
Grid 4 M4 50.62 V/m	
Grid 7 M3 76.91 V/m	

Cursor:

Total = 80.601 V/m E Category: M3 Location: -0.5, 37.5, 4.7 mm

Dipole E-Field measurement/E Scan - CDMA 1/8th 1880_PMF 2/Hearing Aid

Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 30.81 V/m; Power Drift = 0.09 dB PMR not calibrated. PMF = 1.000 is applied. E-field emissions = 30.61 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
28.31 V/m	30.22 V/m	28.54 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
18.23 V/m	20.72 V/m	18.32 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
26.79 V/m	30.61 V/m	30.61 V/m

	isting rvices"		ompatibility RF Emissions T ® Smartphone model RFM12		Page 47 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

Cursor: Total = 30.614 V/m E Category: M4 Location: -3.5, 36, 4.7 mm

Dipole E-Field measurement/E Scan- CW 1880_PMF/Hearing Aid Compatibility

Test (41x181x1): Measurement grid: dx=5mm, dy=5mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 90.26 V/m; Power Drift = -0.02 dB PMR not calibrated. PMF = 1.000 is applied. E-field emissions = 81.58 V/m Near-field category: M3 (AWF 0 dB)

PMF scaled E-field

	Grid 2 M3	
75.79 V/m	78.08 V/m	77.27 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
52.44 V/m	53.31 V/m	51.71 V/m
Grid 7 M3	Grid 8 M3	Grid 9 M3
78.00 V/m	81.58 V/m	79.79 V/m

Cursor:

Total = 81.580 V/m E Category: M3 Location: -0.5, 37.5, 4.7 mm

Dipole E-Field measurement/E Scan - AM80%_ 1880_PMF/Hearing Aid

Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm Reference Value = 56.79 V/m; Power Drift = 0.05 dB PMR not calibrated. PMF = 1.000 is applied. E-field emissions = 52.04 V/m

Near-field category: M4 (AWF 0 dB)

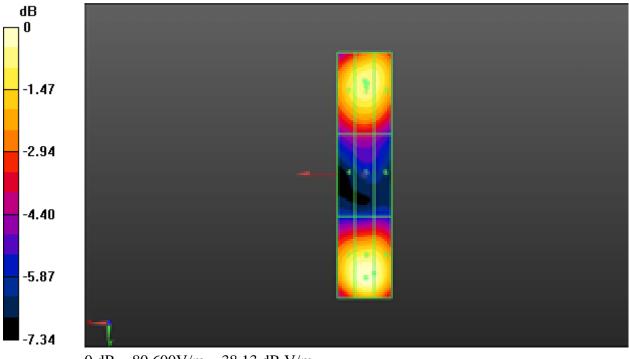
	esting ervices:		ompatibility RF Emissions ⁻ ® Smartphone model RFM1		Page 48 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012	RTS-6026-1304-09	L6ARF	M120LW

PMF scaled E-field

Grid 1 M4 47.54 V/m	Grid 2 M4 49.44 V/m	
Grid 4 M4 33.05 V/m		
Grid 7 M4 49.67 V/m		

Cursor:

Total = 52.041 V/m E Category: M4 Location: -0.5, 37.5, 4.7 mm



0 dB = 80.600 V/m = 38.13 dB V/m

	esting ervices		ompatibility RF Emissions T ® Smartphone model RFM12		Page 49 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

Date/Time: 4/4/2013 2:08:45 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_validation_835 MHz_04_04_13

DUT: HAC-Dipole 835 MHz; Type: CD835V3; Serial: 1011

Communication System: CW; Frequency: 835 MHz Medium parameters used: $\sigma = 0$ S/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Dipole H-Field meausrement with H3DV6 probe/H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid

Compatibility Test (41x181x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.4930 A/m; Power Drift = -0.05 dB

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PMR not calibrated. PMF = 1.000 is applied.

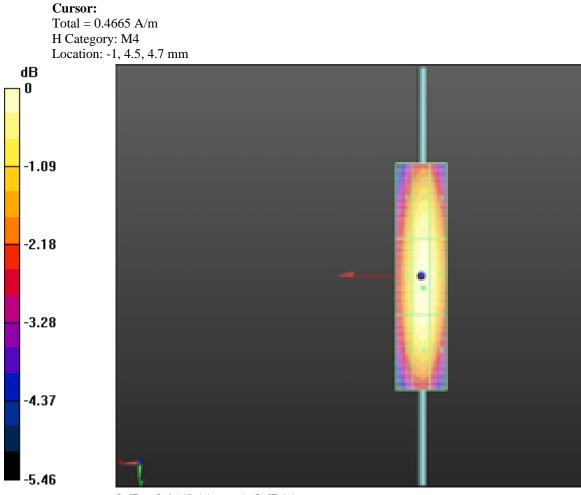
H-field emissions = 0.4665 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-f	ïeld	
Grid 1 M4	Grid 2 M4	Grid 3 M4
0.417 A/m	0.450 A/m	0.442 A/m
Grid 4 M4	Grid 5 M4	Grid 6 ${f M4}$
0.429 A/m	0.466 A/m	0.456 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4

Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW					Page 50 (154)
Author Data	Dates of T		Report No	FCC ID	
Daoud Attayi	Feb. 1	7-29, June 28, 2012	RTS-6026-1304-09	L6ARFI	M120LW
	April (03-04, 2013			

0.426 A/m	0.459 A/m	0.445 A/m
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0 dB = 0.4665 A/m = -6.62 dBA/m

	esting ervices		ompatibility RF Emissions 1 ® Smartphone model RFM12		Page 51 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012)3-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

Date/Time: 6/28/2012 11:48:13 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_PMF_GSM835 MHz_06_28_12

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1011

Communication System: GSM 835_PMF, Communication System: CW, Communication System: AM 80%; Frequency: 835 MHz Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 11/8/2011
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole H-Field measurement with H3DV6 probe/H Scan - GSM 835_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm,

dy=5mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 0.17 V/m; Power Drift = -0.01 dB PMR not calibrated. PMF = 1.000 is applied. H-field emissions = 0.16 A/m Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.15 A/m	0.16 A/m	0.15 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4

P#7		Compatibility RF Emissions Te ry® Smartphone model RFM121	
Author Data	Dates of Test	Report No	FCC ID
Daoud Attayi Feb. 17-29, June 28, 2012 April 03-04, 2013		RTS-6026-1304-09	L6ARFM120LW

0.16 A/m	0.16 A/m	0.16 A/m
Grid 7 ${f M4}$	Grid 8 M4	Grid 9 M4
0.15 A/m	0.16 A/m	0.15 A/m

Cursor:

Total = 0.163 A/m H Category: M4 Location: 0, 8.5, 4.7 mm

Dipole H-Field measurement with H3DV6 probe/H Scan - CW 835_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid:

dx=5mm, dy=5mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 0.28 V/m; Power Drift = 0.08 dB PMR not calibrated. PMF = 1.000 is applied. H-field emissions = 0.47 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field Grid 3 M4 Grid 1 **M4** Grid 2 **M4** 0.44 A/m 0.46 A/m 0.44 A/m Grid 4 M4Grid 6 **M4** Grid 5 M4 0.45 A/m 0.47 A/m 0.45 A/m Grid 7 M4Grid 8 **M4** Grid 9 **M4** 0.45 A/m 0.47 A/m 0.44 A/m

Cursor:

Total = 0.471 A/m H Category: M4 Location: 0, 8, 4.7 mm

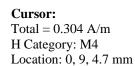
Dipole H-Field measurement with H3DV6 probe/H Scan - AM80%_PMF/Hearing Aid Compatibility Test (41x181x1):

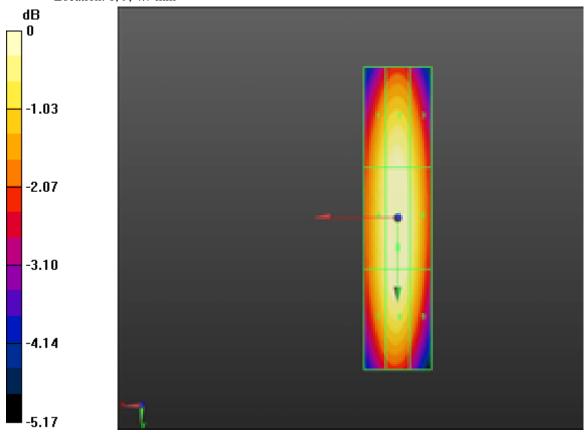
Measurement grid: dx=5mm, dy=5mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 0.32 V/m; Power Drift = 0.12 dB PMR not calibrated. PMF = 1.000 is applied. H-field emissions = 0.30 A/m Near-field category: M4 (AWF 0 dB)

	esting arvices"		Compatibility RF Emissions T r® Smartphone model RFM12		Page 53 (154)
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	April	03-04. 2013			

PMF scaled H-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.28 A/m	0.29 A/m	0.28 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.29 A/m	0.30 A/m	0.29 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.29 A/m	0.30 A/m	0.28 A/m





 $0 \ dB = 0.160 A/m = -15.92 \ dB \ A/m$

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Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

Date/Time: 2/17/2012 4:08:25 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_PMF_UMTS835 MHz_02_17_12

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1011

Communication System: WCDMA FDD V, Communication System: CW, Communication System: AM 80%; Frequency: 835 MHz Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 11/8/2011
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn472; Calibrated: 3/7/2011
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole H-Field measurement with H3DV6 probe/H Scan - UMTS 835_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm,

dy=5mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 0.19 V/m; Power Drift = 0.05 dB PMR not calibrated. PMF = 1.000 is applied. H-field emissions = 0.18 A/m Near-field category: M4 (AWF 0 dB)

	sting rvices*		Compatibility RF Emissions /® Smartphone model RFM1		Page 55 (154)
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PMF scaled H	-field	
Grid 1 M4	Grid 2 M4	Grid 3 M4
0.16 A/m	0.17 A/m	0.16 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.17 A/m	0.18 A/m	0.17 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.17 A/m	0.18 A/m	0.17 A/m

Cursor:

Total = 0.181 A/m H Category: M4 Location: 0.5, 8.5, 4.7 mm

Dipole H-Field measurement with H3DV6 probe/H Scan - CW 835_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid:

dx=5mm, dy=5mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 0.11 V/m; Power Drift = 0.08 dB PMR not calibrated. PMF = 1.000 is applied. H-field emissions = 0.20 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H	-field	
Grid 1 M4	Grid 2 M4	Grid 3 M4
0.17 A/m	0.19 A/m	0.18 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.18 A/m	0.20 A/m	0.19 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.18 A/m	0.19 A/m	0.18 A/m

	ting lices"	Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW		Page 56 (154)	
Author Data Daoud Attayi	Dates of Test Feb. 17-29, June 28, 2012		Report No RTS-6026-1304-09	FCC ID	M120LW
	April (03-04, 2013			

Cursor: Total = 0.197 A/m H Category: M4 Location: -0.5, 1, 4.7 mm

Dipole H-Field measurement with H3DV6 probe/H Scan - AM80%_PMF/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mmDevice Reference Point: 0, 0, -6.3 mm Reference Value = 0.14 V/m; Power Drift = 0.10 dB PMR not calibrated. PMF = 1.000 is applied. H-field emissions = 0.13 A/m

Near-field category: M4 (AWF 0 dB)

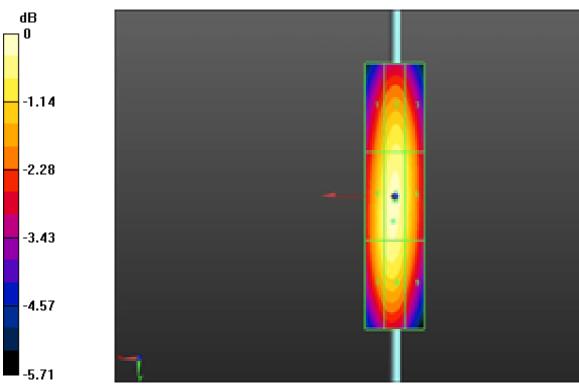
PMF scaled H-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.11 A/m	0.12 A/m	0.12 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.12 A/m	0.13 A/m	0.12 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.12 A/m	0.12 A/m	0.12 A/m

Cursor:

Total = 0.127 A/m H Category: M4 Location: 0, 1.5, 4.7 mm

	ting NCES"	Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW		Page 57 (154)	
Author Data	Dates of T	est	st Report No FCC ID		
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARFI	M120LW



0 dB = 0.180 A/m = -14.89 dB A/m

	ting NCES	Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW		Page 58 (154)	
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012)3-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

Test Laboratory: RIM Testing Services

HAC RF_H-Field_PMF_CDMA835 MHz_02_29_12

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1011

Communication System: CDMA 850, Communication System: CDMA 850 1/8th,

Communication System: CW, Communication System: AM 80%; Frequency: 835 MHz

Medium parameters used: σ = 0 mho/m, ϵ_r = 1; ρ = 0 kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 11/8/2011
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole H-Field meausrement with H3DV6 probe/H Scan - CDMA FR

835_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid:

dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.37 V/m; Power Drift = 0.11 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.34 A/m

Near-field category: M4 (AWF 0 dB)

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	April	03-04, 2013			

PMF scaled H-field

Grid 1 M4 0.32 A/m	
Grid 4 M4 0.33 A/m	
Grid 7 M4 0.32 A/m	

Cursor: Total = 0.344 A/m H Category: M4 Location: 0, 1.5, 4.7 mm

Dipole H-Field meausrement with H3DV6 probe/H Scan - CDMA 1/8th 835_PMF 2/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm,

dy=5mm

Device Reference Point: 0, 0, -6.3 mm Reference Value = 0.13 V/m; Power Drift = 0.09 dB PMR not calibrated. PMF = 1.000 is applied. H-field emissions = 0.13 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.12 A/m		
Grid 4 M4 0.13 A/m		
Grid 7 M4 0.12 A/m	Grid 8 M4	Grid 9 M4

	esting arvices"	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW		Page 60 (154)	
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Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

Cursor: Total = 0.134 A/m H Category: M4 Location: 0, 0, 4.7 mm

Dipole H-Field meausrement with H3DV6 probe/H Scan - CW 835_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm,

dy=5mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 0.39 V/m; Power Drift = 0.08 dB PMR not calibrated. PMF = 1.000 is applied. H-field emissions = 0.35 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.32 A/m	0.34 A/m	0.32 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.34 A/m	0.35 A/m	0.33 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.33 A/m	0.35 A/m	0.33 A/m

Cursor:

Total = 0.355 A/m H Category: M4 Location: 0, 5, 4.7 mm

Dipole H-Field meausrement with H3DV6 probe/H Scan -AM80%_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm,

dy=5mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 0.24 V/m; Power Drift = -0.02 dB PMR not calibrated. PMF = 1.000 is applied. H-field emissions = 0.23 A/m

Near-field category: M4 (AWF 0 dB)

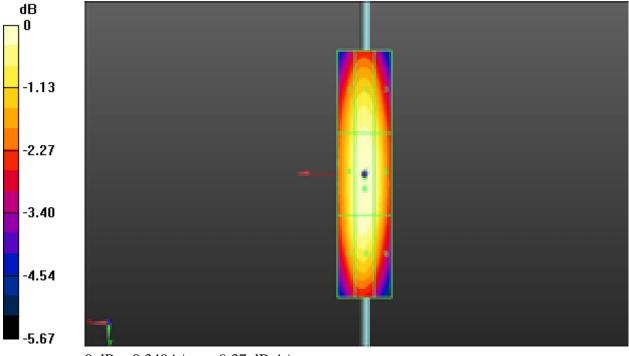
	esting ervices"	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW			Page 61 (154)
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Daoud Attayi		7-29, June 28, 2012	RTS-6026-1304-09	L6ARF	M120LW

PMF scaled H-field

Grid 1 M4 0.20 A/m	
Grid 4 M4 0.21 A/m	
Grid 7 M4 0.21 A/m	

Cursor:

Total = 0.227 A/m H Category: M4 Location: 0, 5.5, 4.7 mm



 $0 \ dB = 0.340 \ A/m = -9.37 \ dB \ A/m$

	esting ervices		ompatibility RF Emissions ⁻ ® Smartphone model RFM1		Page 62 (154)
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Daoud Attayi		17-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

Date/Time: 4/4/2013 2:39:32 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_validation_1880 MHz_04_04_13

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: CW; Frequency: 1880 MHz Medium parameters used: $\sigma = 0$ S/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Dipole H-Field meausrement with H3DV6 probe/H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid

Compatibility Test (41x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.4630 A/m; Power Drift = -0.07 dB

.

PMR not calibrated. PMF = 1.000 is applied.

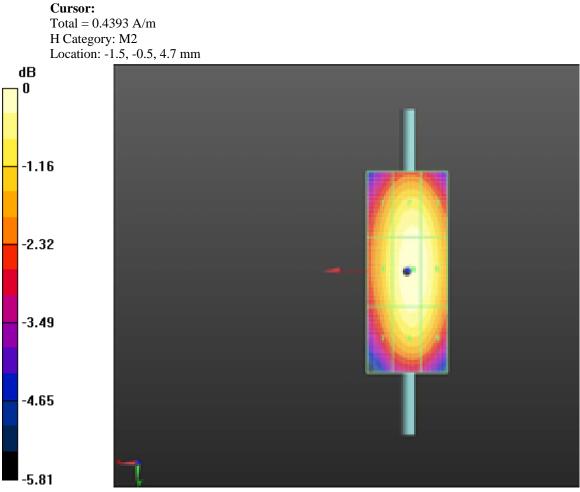
H-field emissions = 0.4393 A/m

Near-field category: M2 (AWF 0 dB)

PMF scaled H	-field	
Grid 1 M2	Grid 2 M2	Grid 3 M2
0.399 A/n	n 0.429 A/m	0.424 A/m
Grid 4 M2	Grid 5 M2	Grid 6 ${ m M2}$
0.407 A/n	0.439 A/m	0.434 A/m
Grid 7 M2	Grid 8 M2	Grid 9 M2

	sting rvices		ompatibility RF Emissions T [®] Smartphone model RFM12		Page 63 (154)
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Daoud Attayi		7-29, June 28, 2012)3-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

0.390 A/m	0.425 A/m	0.418 A/m
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0 dB = 0.4393 A/m = -7.14 dBA/m

	esting ervices"		ompatibility RF Emissions ® Smartphone model RFM1		Page 64 (154)
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Daoud Attayi		17-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

Date/Time: 6/28/2012 12:25:06 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_PMF_GSM1880 MHz_06_28_12

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: GSM 1880_PMF, Communication System: CW, Communication System: AM 80%; Frequency: 1880 MHz Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 11/8/2011
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole H-Field measurement with H3DV6 probe/H Scan -GSM 1880_PMF/Hearing Aid Compatibility Test (41x101x1): Measurement grid: dx=5mm,

dy=5mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 0.11 V/m; Power Drift = -0.01 dB PMR not calibrated. PMF = 1.000 is applied. H-field emissions = 0.11 A/m Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.10 A/m	0.10 A/m	0.10 A/m
Grid 4 ${f M4}$	Grid 5 M4	Grid 6 ${f M4}$

		Aid Compatibility RF Emissions Tes Berry® Smartphone model RFM121L	
Author Data	Dates of Test	Report No	FCC ID
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0.10 A/m	0.11 A/m	0.10 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.10 A/m	0.10 A/m	0.10 A/m

Cursor:

Total = 0.105 A/m H Category: M4 Location: 0, 0.5, 4.7 mm

Dipole H-Field measurement with H3DV6 probe/H Scan - CW 1800_PMF/Hearing Aid Compatibility Test (41x101x1): Measurement

grid: dx=5mm, dy=5mmDevice Reference Point: 0, 0, -6.3 mm Reference Value = 0.32 V/m; Power Drift = 0.00 dB PMR not calibrated. PMF = 1.000 is applied. H-field emissions = 0.30 A/m

Near-field category: M3 (AWF 0 dB)

PMF scaled H-field Grid 1 M3 Grid 3 M3 Grid 2 **M3** 0.28 A/m 0.29 A/m 0.28 A/m Grid 4 **M3** Grid 6 **M3** Grid 5 M3 0.29 A/m 0.30 A/m 0.29 A/m Grid 7 **M3** Grid 8 **M3** Grid 9 **M3** 0.28 A/m 0.29 A/m 0.28 A/m

Cursor:

Total = 0.300 A/m H Category: M3 Location: 0, 1, 4.7 mm

Dipole H-Field measurement with H3DV6 probe/H Scan - AM80%_1880_PMF/Hearing Aid Compatibility Test (41x101x1):

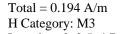
Measurement grid: dx=5mm, dy=5mmDevice Reference Point: 0, 0, -6.3 mm Reference Value = 0.21 V/m; Power Drift = 0.02 dB PMR not calibrated. PMF = 1.000 is applied. H-field emissions = 0.19 A/m Near-field category: M3 (AWF 0 dB)

	esting arvices		ompatibility RF Emissions T ® Smartphone model RFM12		Page 66 (154)
Author Data	Dates of T		Report No	FCC ID	
Daoud Attayi	Feb. 1	7-29, June 28, 2012	RTS-6026-1304-09	L6ARF	M120LW
-	April	03-04. 2013			

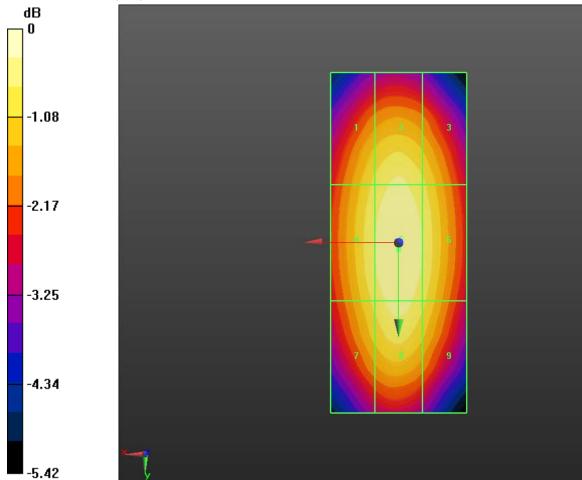
PMF scaled H-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.18 A/m	0.19 A/m	0.18 A/m
Grid 4 M4	Grid 5 M3	Grid 6 M4
0.19 A/m	0.19 A/m	0.19 A/m
Grid 7 M4	Grid 8 M3	Grid 9 M4
0.18 A/m	0.19 A/m	0.18 A/m





Location: 0, 0.5, 4.7 mm



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Daoud Attayi		7-29, June 28, 2012)3-04, 2013	RTS-6026-1304-09	L6ARFI	M120LW

 $0 \ dB = 0.110 \ A/m = -19.17 \ dB \ A/m$

Date/Time: 2/17/2012 3:56:44 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_PMF_UMTS1880 MHz_02_17_12

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: WCDMA FDD II, Communication System: CW, Communication System: AM 80%; Frequency: 1880 MHz Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 11/8/2011
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn472; Calibrated: 3/7/2011
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole H-Field measurement with H3DV6 probe/H Scan -UMTS 1880_PMF/Hearing Aid Compatibility Test (41x101x1): Measurement grid: dx=5mm,

dy=5mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 0.16 V/m; Power Drift = 0.06 dB PMR not calibrated. PMF = 1.000 is applied. H-field emissions = 0.15 A/m Near-field category: M4 (AWF 0 dB)

	esting ervices		ompatibility RF Emissions T ® Smartphone model RFM12		Page 68 (154)
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Daoud Attayi	Feb. 1	7-29, June 28, 2012	RTS-6026-1304-09	L6ARF	M120LW
-	April (03-04. 2013			

PMF scaled H-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.14 A/m	0.14 A/m	0.14 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.14 A/m	0.15 A/m	0.14 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.14 A/m	0.15 A/m	0.14 A/m

Cursor:

Total = 0.150 A/m H Category: M4 Location: 0, 0.5, 4.7 mm

Dipole H-Field measurement with H3DV6 probe/H Scan - CW 1880_PMF/Hearing Aid Compatibility Test (41x101x1): Measurement

grid: dx=5mm, dy=5mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 0.16 V/m; Power Drift = -0.01 dB PMR not calibrated. PMF = 1.000 is applied. H-field emissions = 0.15 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H	-field	
Grid 1 M4	Grid 2 M4	Grid 3 ${f M4}$
0.14 A/m	0.14 A/m	0.14 A/m
Grid 4 ${f M4}$	Grid 5 M4	Grid 6 ${f M4}$
0.14 A/m	0.15 A/m	0.14 A/m
Grid 7 ${f M4}$	Grid 8 M4	Grid 9 M4
0.14 A/m	0.15 A/m	0.14 A/m

	ting vices"	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW		Page 69 (154)	
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

Cursor: Total = 0.149 A/m H Category: M4 Location: 0, 0.5, 4.7 mm

Dipole H-Field measurement with H3DV6 probe/H Scan - AM80%_1880_PMF/Hearing Aid Compatibility Test (41x101x1):

Measurement grid: dx=5mm, dy=5mmDevice Reference Point: 0, 0, -6.3 mm Reference Value = 0.10 V/m; Power Drift = -0.07 dB PMR not calibrated. PMF = 1.000 is applied. H-field emissions = 0.10 A/m

Near-field category: M4 (AWF 0 dB)

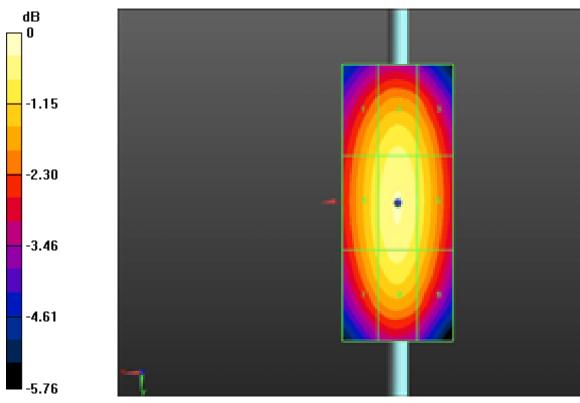
PMF scaled H-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.09 A/m	0.09 A/m	0.09 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.09 A/m	0.10 A/m	0.09 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.09 A/m	0.09 A/m	0.09 A/m

Cursor:

Total = 0.096 A/m H Category: M4 Location: 0, 0, 4.7 mm

	ting NCES"	Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW		Page 70 (154)	
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-	April (03-04, 2013			



0 dB = 0.150 A/m = -16.48 dB A/m

	ting NCES"	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW		Page 71 (154)	
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

Test Laboratory: RIM Testing Services

HAC RF_H-Field_PMF_CDMA1880 MHz_02_29_12

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: CDMA 1900, Communication System: CDMA 1900 1/8th,

Communication System: CW, Communication System: AM 80%; Frequency: 1880 MHz

Medium parameters used: σ = 0 mho/m, ϵ_r = 1; ρ = 0 kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 11/8/2011
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole H-Field meausrement with H3DV6 probe/H Scan -CDMA FR

1880_PMF/Hearing Aid Compatibility Test (41x101x1): Measurement grid:

dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.31 V/m; Power Drift = -0.05 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.29 A/m

Near-field category: M3 (AWF 0 dB)

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	April (03-04, 2013			

PMF scaled H-field

Grid 1 M3 0.27 A/m	
Grid 4 M3 0.28 A/m	
Grid 7 M3 0.27 A/m	

Cursor: Total = 0.293 A/m H Category: M3 Location: 0, -0.5, 4.7 mm

Dipole H-Field meausrement with H3DV6 probe/H Scan -CDMA 1/8th 1880_PMF 2/Hearing Aid Compatibility Test (41x101x1): Measurement grid: dx=5mm,

dy=5mm

Device Reference Point: 0, 0, -6.3 mm Reference Value = 0.12 V/m; Power Drift = -0.90 dB PMR not calibrated. PMF = 1.000 is applied. H-field emissions = 0.11 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 0.10 A/m	
Grid 4 M4 0.10 A/m	
Grid 7 M4 0.09 A/m	

	esting arvices		ompatibility RF Emissions T ® Smartphone model RFM12		Page 73 (154)
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Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

Cursor: Total = 0.111 A/m H Category: M4 Location: 0, 0, 4.7 mm

Dipole H-Field meausrement with H3DV6 probe/H Scan - CW 1880_PMF/Hearing Aid Compatibility Test (41x101x1): Measurement grid: dx=5mm,

dy=5mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 0.31 V/m; Power Drift = -0.01 dB PMR not calibrated. PMF = 1.000 is applied. H-field emissions = 0.29 A/m

Near-field category: M3 (AWF 0 dB)

PMF scaled H-field

Grid 1 M3	Grid 2 M3	Grid 3 M3
0.27 A/m	0.28 A/m	0.27 A/m
Grid 4 M3	Grid 5 M3	Grid 6 M3
0.28 A/m	0.29 A/m	0.28 A/m
Grid 7 M3	Grid 8 M3	Grid 9 M3
0.27 A/m	0.28 A/m	0.26 A/m

Cursor:

Total = 0.289 A/m H Category: M3 Location: 0, 0, 4.7 mm

Dipole H-Field meausrement with H3DV6 probe/H Scan -AM80%_1880_PMF/Hearing Aid Compatibility Test (41x101x1): Measurement grid:

dx=5mm, dy=5mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 0.20 V/m; Power Drift = 0.04 dB PMR not calibrated. PMF = 1.000 is applied. H-field emissions = 0.19 A/m

Near-field category: M4 (AWF 0 dB)

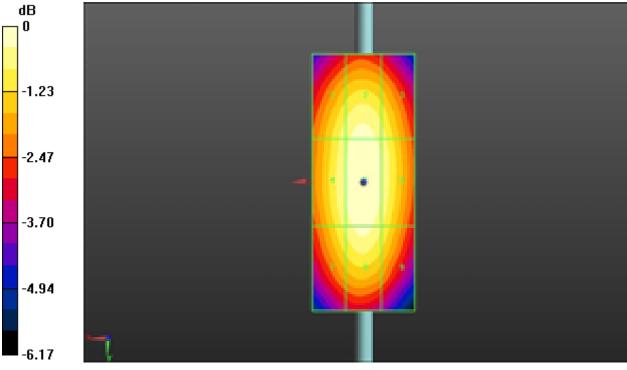
	esting ervices		ompatibility RF Emissions ® Smartphone model RFM1		Page 74 (154)
Author Data	Dates of T	est	Report No	FCC ID	
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PMF scaled H-field

Grid 1 M4 0.17 A/m	
Grid 4 M4 0.18 A/m	
Grid 7 M4 0.17 A/m	

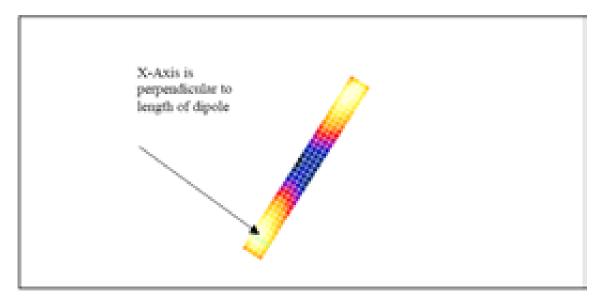
Cursor:

Total = 0.187 A/m H Category: M4 Location: 0, 0, 4.7 mm



0 dB = 0.290 A/m = -10.75 dB A/m

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The green line in this figure shows the axis along which the points lie.

Comparison of 5mm and 2mm step sizes

An additional set of measurements was taken: dipole validations were performed using 5mm and 2mm step sizes. The deba between the two readings is insignificant for both field types (< 0.4% for E and 0% for H), demonstrating that 5mm is sufficient. The plots follow.

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Date/Time: 14/17/2005 11:25/24 AM

Late RIM Testing Services (RTS)

Dipole Validation 1880 MHz_E-Field 07_14_05

DUT: HAC Dipole 1990 Mills; Type: CD199033

Communication System: CW: Frequency: 1880 MHz:Daty Cycle: 1:3 Medium: Air Medium parameters used: n = 0 mbolm, n_p = 1: p = 1000 kg/m³ Phantom section: II Device Section

DASY1 Configuration:

- Piche: ER3DV6 SN2285: ConstF(1, 1, 1); Calibrated: 1012/2101
- Sensor-Surface them (Fis Surface)Sensor-Surface: (Fis Surface)
- Electronics: DAID So472; Calibrated: 03/01/2016
- Phantom: EAC Test Arabi Type: SD HAC P91 BA:
- Meanagement SW: DASY4, V4.5 Build PP, Postprocessing SW: SEMCAD, V1.8 Build 146-

E Scan Humm above CD 1880 MHz/Hearing Aid Compatibility Test (5s19s1):

Massaransen prid: dx:/Smm, dy:/Smm Masimum value of Total Imeasurab = 134,8 Y/m

E Scan Humm above CD 1880 MHz/Hearing Aid Compatibility Test (41x181x1):

Memorement prid: dv=5mm, dy=5mm Maximum value of Total field (slot averaged) = 131.0 V/m Hearing Aid Near-Field Category: M2 (AWF 0.0B)

	U in Yim)	(Time anotage	 E in Visu. 	(Net averaged):
--	-----------	---------------	--------------------------------	-----------------

Grid 1	Ge63.2	COM 3	Geld 1	Geld 2	660
123.2	1,38,1	138.4	123.2	138.1	138.4
Cold 6	Crist 2	(arid))	Crid 6	Citid N	Gend He
9.8.9	6.29	12.29	80.9	6.0	92.2
Cold 7	Celd N	Calif. 7	Calid 7	Ceid 8	Gend P
112.5	131.0	130.7	112.8	131.0	1,30.7

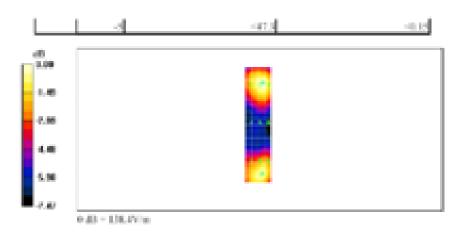
Canopary	AWFIGHT	Limits for E-Fight Emissions (Virus)	Limits for H-Fight Emissions (Arm)
541	- 0	195.5 - 351.5	0.5-1.02
	5	125,6 - 256,1	4.43 - 43
942	6	112.2 - 199.5	0,31.04
		84.1 - 189.5	0.25 - 0.45
10	- 0	63.1-112.2	0,19~0,34
		47.3 - 81.1	0.15 - 0.25
3.44	0	-163.2	-10.19

fler/CrProgram%2018er/D/SY14Prin_Lauplane/Dipole%20Validation%20180%20... 1447/2005

	ting NCES"		ompatibility RF Emissions Te Smartphone model RFM12 ⁴		Page 77 (154)
Author Data	Dates of T	est	Report No	FCC ID	
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file/C/Program%2011er/D/OY1Prin_Template/Dipole%2014/datioe%20180%20., 14072005

		Compatibility RF Emissions Te y® Smartphone model RFM12		Page 78 (154)
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Daoud Attayi	Feb. 17-29, June 28, 2012 April 03-04, 2013	RTS-6026-1304-09	LGARFI	M120LW

Date/Time: 1407/2005 11:14/51 AM

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Date/Time: 14/192005 11:44:51 AM

Late RIM Testing Services (RTS)

Dipole Validation 1880 MHz_2mm step_E-Field 07_14_05

DUT: HAC Dipole 1980 Mills; Type: CD198033

Communication System: CW: Frequency: 1880 MHz:Daty Cycle: 1:3 Medium: Air Medium parameters used: n = 0 mbolm, n_p = 1: p = 1000 kg/m³ Phantom section: II Device Section

DASY1 Configuration:

- Piche: ER3DV6 SN2285: ConstF(1, 1, 1); Calibrated: 1012/2101
- Senser-Surface from (Fis Surface)Senser-Surface (Fis Surface)
- Electronics: DAE3 Sn472; Calibrated: 03/01/2016
- Phantom: EAC Test Arabi Type: SD HAC P91 BA:
- Meanagement SW: DASY4, V4.5 Build PP, Postprocessing SW: SEMCAD, V1.8 Build 146-

E Scan Humm above CD 1880 MHz/Hearing Aid Compatibility Test (11v0is1):

Massaransen pild: dv: 2mm, dy: 2mm Masimum value of Total (measuredr = 138,9 V/m

E Scan Humm above CD 1880 MHz/Hearing Aid Compatibility Test (101x451x1):

Memorement prid: dv=2mm, dy=2mm Maximum value of Total field (slot averaged) = 131.2 Vite Hearing Aid Near-Field Category: M2 (AWF 0.0B)

E in Yim (Eine avoraged) E in Vin (Not avorage)	$U \approx V \approx$	(These arrow	J fleep	in Mires	Net reency	eth:
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Geld 1	G482	GAU3	Gald 3	GAU2	GS23
123-1	1,98,6	138.6	123.0	1384	138.6
cesa e	Ceid 2	0.030	Crist A	Conid ()	Gendre
MLA	92.8	91.4	NLA	912-1	91.6
Geid 7	0413	0317	0847	054.8	Gand 9
121.3	0312	121.0	131.2	131.2	131.0

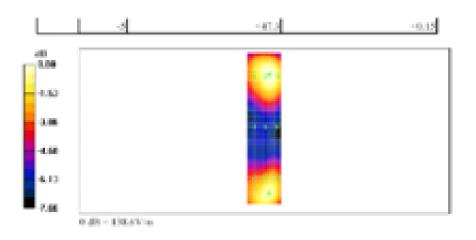
Canopary	AWFIGHT	Limits for E-Fight Emissions (Virus)	Limits for H-Fight Emissions (Arm)
541	- 0	195.5 - 351.5	0.5-1.02
	5	849.6 - 266.1	4.43 - 43
942	6	112.2 - 199.5	0,31.04
		84.1 - 189.5	0.25 - 0.45
10	- 0	63.1-112.2	0,19~0,34
		47.3 - 81.1	0.15 - 0.25
3.44	0	-163.2	-10.19

BerC/Program/2018er/DASY4Prist, Templater/Dipole/2019aldation/201887-28. 1447/2005

P#75	ting vices:	Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW			Page 79 (154)
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	lesting ervices	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW			Page 80 (154)
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Daoud Attayi		7-29, June 28, 2012)3-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

Date/Time: 14/07/2005 12:40:00 PM

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Date/Time: 141022005 12:4840 PM

Lals: RIM Testing Services (RTS)

ILAC_H_Dipole_CW 1880_5 mm step_07_14_05

BUT: HAC Dipole 1880 Mille; Type: CD4880V3

Communication System: CW: Frequency: IBB0 Mile:Duty Cycle: I:1 Mediane Air Median parameters used: $\sigma = 0$ mbolm, $c_0 = 1$; $\rho = 1$ kg/m² Prantom sections II Dipole Section

DASY14 Configuration:

- Piche: 1085/6 556115; ; Calibrand: 1012/2004
- Senser-Surface: from (Fis Surface)Sensor-Surface: (Fis Surface)
- Electronics: DALJ Sol72; Calibrated: 03/01/2005
- Phantom: HAC Test Arab; Type: SD HAC POI BA:
- Meanagement SW: DANY4, VL5 Build FR: Postproceeding SW: SEMEAD, VL8 Build 145

II Scan 19mm above CD 1880 MILeHearing Aid Compatibility Test (5s19s1):

Messerement grid: dv=5mm, dy=5mm Maximum value of Tenal (measured) = 0.406 A/m

H Sean Dham above CD 1880 MHz/Hearing Aid Compatibility Test (41x181x1): Manarament grid; dv-Sam, dy-Sam

Maximum value of Total field (slot avaraged) = 0.408 A/m

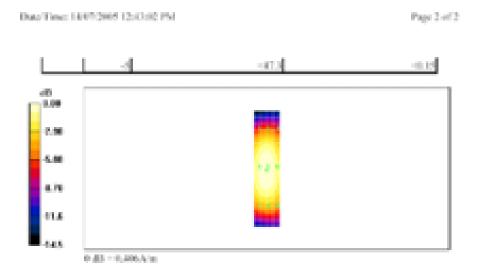
Bearing Aid Near-Field Category: M2 (AWF 0 dB)

H in Ain (Time averaged)	Hin Ain (Net averapel)
GMTGM2GM3	GM1GM2GM3
0.342 0.399 0.344	0.342 0.359 0.344
Grid 4 Grid 2 Grid 6	Cried & Cried 5 Grind 6
0.389 8.486 0.389	0,1998,406 0,389
Grid 7 Grid N Grid 9	Celid 7 Celid 8 Geld 9
0.363 0.378 0.363	0.363/0.378/0.363

Catogory	1,947 (48)	Limits for E-Field Emissions (Wind	Limits for H-Field Emissions (Arm)
MI		195,5 - 354,8	9,6 - 1,87
		14%a - 256.1	9.45 - 0.8
142		112.2 - 199.5	9,34 - 0.8
	1	84.1-189.5	625-6.6
10	- 0	43.1 - 112.2	0,19 - 0,34
		47.3 - 84.1	0.150.25
144		- 63.1	-0.15

BerC/Prepart/2018e/DASY4Prix_Tenplace/DAC_JL/Dpik_CW520180_2%...1407203

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Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW



file:/C:Poguar%2018.o/DASY4Prin_Templace/UAC_II_Dipole_C%%21180_2%...1407205

	esting ervices"	Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW			
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Date/Time: 1447/2005 12:53:40-PM

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Date/Time: 14/07/2005 12:53:40 PM

Late RIM Testing Services (RTS)

HAC_H_Dipole_CW 1880_2 mm step_07_14_05

DUT: HAC Dipole 1990 Mills; Type: CD199033

Communication System: CW: Frequency: 1880 MilesDaty Cycle: 1:1 Medium: Air Medium parameters used: n =0 miles/m, n_p = 1: p = 1 kg/m³ Phantom section: II Dipole Section

DASY11 Configuration:

- Picha: 108946 SN6105; ; Calibrated: 1012/2004
- Senser-Surface from (Fis Surface)Senser-Surface (Fis Surface)
- Electronics: DAEJ Sol72; Calibrated: 03/01/2015
- Phantom: EAC Test Arabi Type: SD HAC P91 BA:

- Meanagement SW: DASY4, V4.5 Build PP, Postprocessing SW: SEMCAD, V1.8 Build 146-

H Scan 19mm above CD 1880 MHz/Hearing Aid Compatibility Test (11x/6s1):

Massaransen pid: dv: 2mm, dy: 2mm Masimum value of Total (measuredr = 0.406 A/m

H Sean Dumn above CD 1880 MHz/Hearing Aid Compatibility Test (101x451x1):

Memoryment grid: dv-2mm, dy-2mm Maximum value of Total field (slot averaged) = 0.406. A/m Hearing Aid Near-Field Category: M2 (AWF 0.48)

If in A/m (Time avoraged). If in A/m (Slot avoraged)

G631	6692	GAU 3	G481	0.822	G(31)
9.347	6361	0,348	6,347	0.361	6,348
0.594	Gend ()	Crist IS	Crist 6	0.496	Gend H
0.394	0.406	10.391	0.394	0.496	0.390
Casa 7 8,367	Geg 8 0.390	043 9 8,345	0447 6,347	Crid 8 0.390	6.365

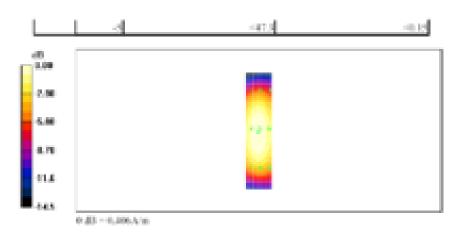
Canopary	AWFIGHT	Limits for E-Field Emissions (Vited	Limits for H-Field Embalant (Amc)
541	0	195.5 - 351.5	0.6 - 1.05
	5	141.6 - 256.1	6.0 - 13
342	0	112.2 - 199.5	0,340.6
		84.1 - 119.5	0.25 - 0.45
4.5	- 0	63.1-112.2	0.19-0.34
	5	47.3 - 84.1	0.15 - 0.25
144	6	<53.1	-0.19

BerCProgun%20EeiDASY4Prist_Leuplac/DAC_E_Dip-le_C%%201886_2%. 1447/2005

	ting NCES"	Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW			Page 83 (154)
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A.3 RF emission field plots

	êsting ervices		ompatibility RF Emissions T ® Smartphone model RFM12		Page 85 (154)
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Date/Time: 4/4/2013 12:27:38 AM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_GSM850

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 303E5577

Communication System: GSM 850; Frequency: 824.2 MHz, Frequency: 836.8 MHz, Frequency: 848.8 MHz Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 SN2286; ConvF(1, 1, 1); Calibrated: 1/11/2013;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to Device_Low_Chan/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 47.33 V/m; Power Drift = -0.00 dB PMR not calibrated. PMF = 3.000 is applied. E-field emissions = 120.4 V/m Near-field category: M4 (AWF -5 dB)

PMF scaled E-fi	ield	
Grid 1 M4	Grid 2 $M4$	Grid 3 M4
101.8 V/m	116.8 V/m	116.8 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
101.9 V/m	120.4 V/m	120.4 V/m

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3.12	lesting	ompatibility RF Emissions To ® Smartphone model RFM12	Page

Grid 7 ${f M4}$	Grid 8 M4	Grid 9 M4
103.8 V/m	119.4 V/m	119.3 V/m

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_Mid_Chan/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm Reference Value = 45.47 V/m; Power Drift = -0.06 dB PMR not calibrated. PMF = 3.000 is applied. E-field emissions = 120.8 V/m

Near-field category: M4 (AWF -5 dB)

PMF scaled E	-field	
Grid 1 M4	Grid 2 M4	Grid 3 M4
90.83 V/n	n 113.4 V/m	113.4 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
96.15 V/n	n 120.8 V/m	120.9 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
103.0 V/n	n 121.7 V/m	121.7 V/m

Cursor:

Total = 121.7 V/m E Category: M4 Location: -8.5, 19.5, 8.7 mm

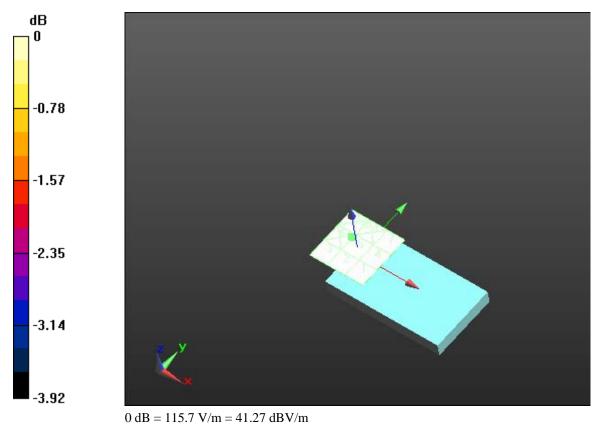
Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_High_Chan/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm Reference Value = 50.15 V/m; Power Drift = -0.01 dB PMR not calibrated. PMF = 3.000 is applied. E-field emissions = 133.8 V/m Near-field category: M4 (AWF -5 dB)

PMF scaled E-field

	êsting ervices	0	ompatibility RF Emissions 1 ® Smartphone model RFM12		Page 87 (154)
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Grid 1 M4	Grid 2 M4	Grid 3 M4
101.2 V/m	127.5 V/m	127.6 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
105.9 V/m	133.8 V/m	134.0 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
111.3 V/m	133.7 V/m	133.8 V/m



	sting vices		ompatibility RF Emissions To ® Smartphone model RFM12		Page 88 (154)
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Daoud Attayi		7-29, June 28, 2012)3-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

Date/Time: 4/4/2013 12:41:27 AM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_GSM850-Telecoil

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 303E5577

Communication System: GSM 850; Frequency: 848.8 MHz Medium parameters used: $\sigma = 0$ S/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

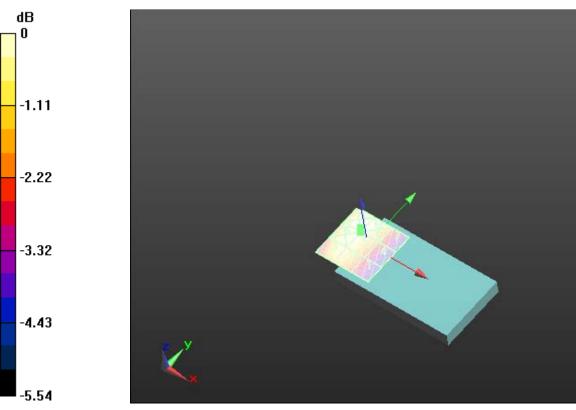
- Probe: ER3DV6 SN2286; ConvF(1, 1, 1); Calibrated: 1/11/2013;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from **Probe Center to the Device telecoil/Hearing Aid Compatibility Test (101x101x1):**

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 49.68 V/m; Power Drift = -0.09 dBPMR not calibrated. PMF = 3.000 is applied. E-field emissions = 129.0 V/mNear-field category: M4 (AWF -5 dB)

 PMF scaled E-f	ïeld	
Grid 1 M4	Grid 2 M4	Grid 3 M4
95.92 V/m	120.5 V/m	121.2 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
99.56 V/m	129.0 V/m	130.2 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
101.5 V/m	129.5 V/m	130.6 V/m

	ësting ervices:		ompatibility RF Emissions T ® Smartphone model RFM12		Page 89 (154)
Author Data	Dates of T		Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW



 $0 \; dB = 125.4 \; V/m = 41.97 \; dBV/m$

	ting vices		ompatibility RF Emissions Te Smartphone model RFM12		Page 90 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

Date/Time: 4/4/2013 1:27:02 AM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_UMTS_Band_V

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 303E5577

Communication System: WCDMA FDD V; Frequency: 826.4 MHz, Frequency: 836.4 MHz, Frequency: 846.6 MHz Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 SN2286; ConvF(1, 1, 1); Calibrated: 1/11/2013;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to Device_Low_Chan/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 55.00 V/m; Power Drift = -0.11 dB

PMR not calibrated. PMF = 1.070 is applied.

E-field emissions = 50.73 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-f	ield	
Grid 1 M4	Grid 2 M4	Grid 3 M4
41.04 V/m	48.82 V/m	48.56 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
42.29 V/m	50.73 V/m	50.40 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4

sting rvices"				Page 91 (154)
		Report No	FCC ID	
		RTS-6026-1304-09	L6ARFI	M120LW
	Feb. 1	Annex A to Hearing Aid C	Annex A to Hearing Aid Compatibility RF Emissions To Report for the BlackBerry® Smartphone model RFM12	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW Dates of Test Report No FCC ID Feb. 17-29, June 28, 2012 RTS-6026-1304-09 FCC ID

42.64 V/m 50.39 V/m 50.12 V/m

Cursor:

Total = 50.73 V/m E Category: M4 Location: -6, 5, 8.7 mm

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_Mid_Chan/Hearing Aid

Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm Reference Value = 54.74 V/m; Power Drift = 0.06 dB PMR not calibrated. PMF = 1.070 is applied. E-field emissions = 52.15 V/m

Near-field category: M4 (AWF 0 dB)

 PMF scaled E-f	ield	
Grid 1 ${f M4}$	Grid 2 M4	Grid 3 M4
39.36 V/m	49.28 V/m	49.34 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
41.53 V/m	52.15 V/m	52.17 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
44.29 V/m	52.39 V/m	52.37 V/m

Cursor:

Total = 52.39 V/m E Category: M4 Location: -8, 19.5, 8.7 mm

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_High_Chan/Hearing Aid

Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm Reference Value = 53.14 V/m; Power Drift = 0.01 dB PMR not calibrated. PMF = 1.070 is applied. E-field emissions = 50.03 V/m Near-field category: M4 (AWF 0 dB)

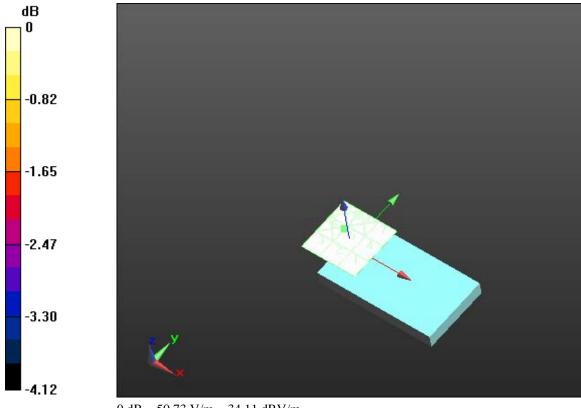
	esting ervices"		ompatibility RF Emissions 1 ® Smartphone model RFM12		Page 92 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

PMF scaled E-fie	ld
------------------	----

Grid 1 M4	Grid 2 M4	Grid 3 M4
39.02 V/m	47.71 V/m	47.73 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
40.53 V/m	50.03 V/m	50.04 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
42.40 V/m	49.82 V/m	49.82 V/m



Total = 50.04 V/m E Category: M4 Location: -9, 5, 8.7 mm



0 dB = 50.73 V/m = 34.11 dBV/m

		id Compatibility RF Emissions Te erry® Smartphone model RFM121	
Author Data	Dates of Test	Report No	FCC ID
Daoud Attayi	Feb. 17-29, June 28, 2012 April 03-04, 2013	RTS-6026-1304-09	L6ARFM120LW

Date/Time: 4/4/2013 1:57:49 AM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_UMTS_Band_V-Telecoil

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 303E5577

Communication System: WCDMA FDD V; Frequency: 836.4 MHz Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

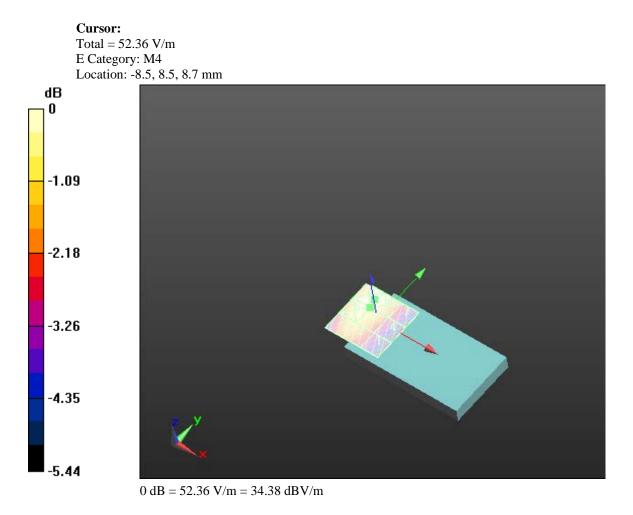
- Probe: ER3DV6 SN2286; ConvF(1, 1, 1); Calibrated: 1/11/2013;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_telecoil/Hearing Aid Compatibility Test (101x101x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mmDevice Reference Point: 0, 0, -6.3 mm Reference Value = 55.39 V/m; Power Drift = -0.07 dB PMR not calibrated. PMF = 1.070 is applied. E-field emissions = 51.04 V/m Near-field category: M4 (AWF 0 dB)

PMF scaled E-f	ield	
Grid 1 M4	Grid 2 M4	Grid 3 M4
37.65 V/m	46.99 V/m	47.22 V/m
Grid 4 M4	Grid 5 M4	Grid 6 ${f M4}$
39.74 V/m	51.04 V/m	51.57 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
41.02 V/m	52.15 V/m	52.36 V/m

	sting rvices*		ompatibility RF Emissions ⁻ ® Smartphone model RFM1		Page 94 (154)
Author Data	Dates of T		Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW



	êsting ervices		ompatibility RF Emissions T ® Smartphone model RFM12		Page 95 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

Date/Time: 4/4/2013 12:51:40 AM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_GSM1900

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 303E5577

Communication System: GSM 1900; Frequency: 1850.2 MHz, Frequency: 1880 MHz, Frequency: 1909.8 MHz Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 SN2286; ConvF(1, 1, 1); Calibrated: 1/11/2013;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to Device_Low_Chan/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 19.36 V/m; Power Drift = 0.10 dB

PMR not calibrated. PMF = 2.850 is applied.

E-field emissions = 57.97 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-f	ield	
Grid 1 M3 55.60 V/m	Grid 2 M3 57.97 V/m	Grid 3 M3 55.05 V/m
Grid 4 M4 40.72 V/m	Grid 5 M3 50.10 V/m	Grid 6 M3 50.21 V/m
Grid 7 ${f M4}$	Grid 8 M3	Grid 9 M3

P\$	ting NCES"		ompatibility RF Emissions Te Smartphone model RFM12		Page 96 (154)
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Daoud Attayi		7-29, June 28, 2012)3-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

43.87 V/m 60.05 V/m 60.06 V/m

Cursor:

Total = 60.06 V/m E Category: M3 Location: -9, 25, 8.7 mm

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_Mid_Chan/Hearing Aid

Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm Reference Value = 19.21 V/m; Power Drift = 0.21 dBPMR not calibrated. PMF = 2.850 is applied. E-field emissions = 58.41 V/m

Near-field category: M3 (AWF -5 dB)

_	PMF scaled E-f	ield	
	Grid 1 M3	Grid 2 M3	Grid 3 M3
	51.22 V/m	53.98 V/m	53.21 V/m
ſ	Grid 4 ${f M4}$	Grid 5 M3	Grid 6 M3
	36.12 V/m	58.41 V/m	58.88 V/m
ſ	Grid 7 M3	Grid 8 M3	Grid 9 M3
	50.86 V/m	71.66 V/m	71.59 V/m

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_High_Chan/Hearing Aid

Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 18.00 V/m; Power Drift = 0.12 dB

PMR not calibrated. PMF = 2.850 is applied.

E-field emissions = 68.61 V/m

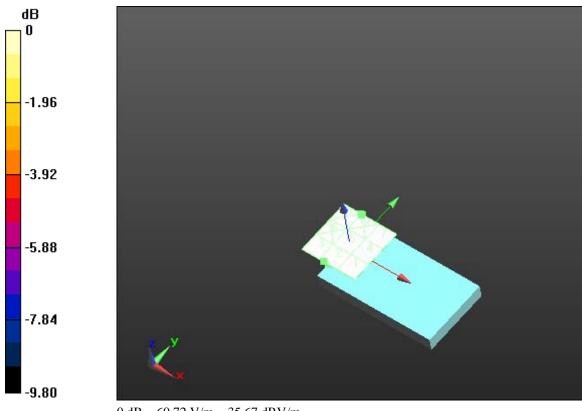
Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

Grid 1 M3 Grid 2 M3 Grid 3 M3
--

	ting vices:		ompatibility RF Emissions Te 9 Smartphone model RFM12		Page 97 (154)
Author Data	Dates of T	est	Report No	FCC ID	
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63.09 V/m	68.61 V/m	68.46 V/m
Grid 4 M4	Grid 5 M3	Grid 6 M3
41.18 V/m	54.45 V/m	55.54 V/m
Grid 7 M3	Grid 8 M3	Grid 9 M3
52.32 V/m	74.57 V/m	74.56 V/m



 $^{0 \;} dB = 60.72 \; V/m = 35.67 \; dB V/m$

Author Data Dates of Test Report No. FCC ID			Page 98 (154)		
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

Date/Time: 4/4/2013 3:04:32 AM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_GSM1900-Telecoil

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 303E5577

Communication System: GSM 1900; Frequency: 1909.8 MHz Medium parameters used: $\sigma = 0$ S/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

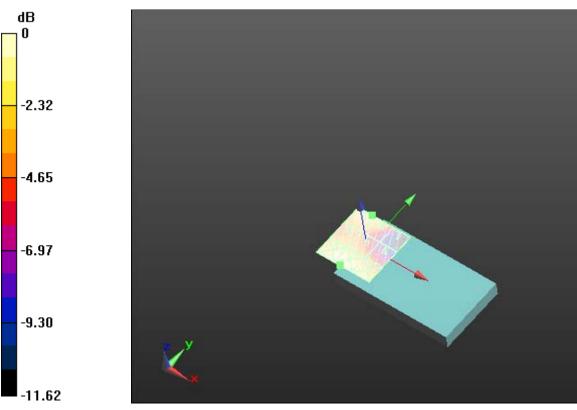
- Probe: ER3DV6 SN2286; ConvF(1, 1, 1); Calibrated: 1/11/2013;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from **Probe Center to the Device telecoil/Hearing Aid Compatibility Test (101x101x1):**

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 17.27 V/m; Power Drift = 0.02 dBPMR not calibrated. PMF = 2.850 is applied. E-field emissions = 65.40 V/mNear-field category: M3 (AWF -5 dB)

PMF scaled E-fi	ield	
Grid 1 M3	Grid 2 M3	Grid 3 M3
65.60 V/m	70.55 V/m	69.61 V/m
Grid 4 M4	Grid 5 M3	Grid 6 M3
46.02 V/m	52.74 V/m	52.67 V/m
Grid 7 M4	Grid 8 M3	Grid 9 M3
38.42 V/m	64.21 V/m	65.40 V/m

	ësting ervices:		ompatibility RF Emissions 1 [®] Smartphone model RFM12		Page 99 (154)
Author Data	Dates of T		Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW



 $0 \; dB = 71.32 \; V/m = 37.06 \; dB V/m$

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Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARFI	W120LW

Date/Time: 4/4/2013 3:09:14 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_GSM1900_2100mA_Battery

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 303E5577

Communication System: GSM 1900; Frequency: 1909.8 MHz Medium parameters used: $\sigma = 0$ S/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 SN2286; ConvF(1, 1, 1); Calibrated: 1/11/2013;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_High_Chan_2100mA_Battery/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 16.31 V/m; Power Drift = 0.10 dB

PMR not calibrated. PMF = 2.850 is applied.

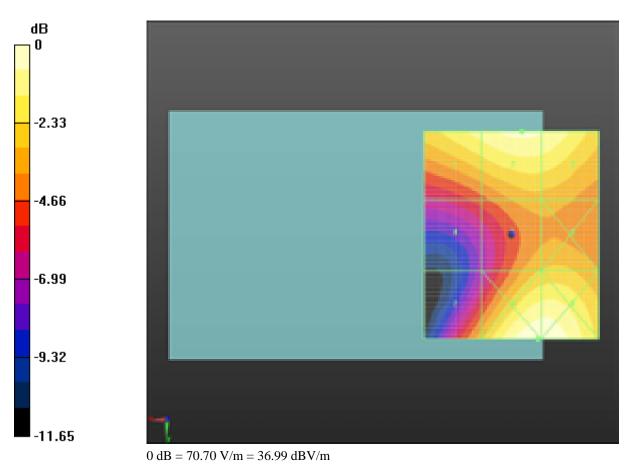
E-field emissions = 66.49 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-fi	eld	
Grid 1 M3	Grid 2 M3	Grid 3 M3
61.72 V/m	66.49 V/m	65.14 V/m
Grid 4 M4	Grid 5 M3	Grid 6 M3
40.05 V/m	49.83 V/m	50.90 V/m
Grid 7 M3	Grid 8 M3	Grid 9 M3

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Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARFI	M120LW





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Author Data					
Daoud Attayi		7-29, June 28, 2012	RTS-6026-1304-09	L6ARFN	/1120LW
	April	03-04, 2013			

Date/Time: 4/4/2013 2:13:24 AM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_UMTS_Band_II

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 303E5577

Communication System: WCDMA FDD II; Frequency: 1852.4 MHz, Frequency: 1880 MHz, Frequency: 1907.6 MHz Medium parameters used: $\sigma = 0$ S/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 SN2286; ConvF(1, 1, 1); Calibrated: 1/11/2013;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to Device_Low_Chan/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 29.03 V/m; Power Drift = -0.01 dB

PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 28.91 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-f	ield	
Grid 1 M4	Grid 2 M4	Grid 3 M4
27.31 V/m	28.91 V/m	28.55 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
19.63 V/m	27.55 V/m	27.56 V/m
Grid 7 ${f M4}$	Grid 8 M4	Grid 9 M4

	ting NCES"		ompatibility RF Emissions To ® Smartphone model RFM12		Page 103 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012)3-04, 2013	RTS-6026-1304-09	L6ARFI	M120LW

26.66 V/m 34.86 V/m 34.77 V/m

Cursor:

Total = 34.86 V/m E Category: M4 Location: -7, 25, 8.7 mm

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_Mid_Chan/Hearing Aid

Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm Reference Value = 28.84 V/m; Power Drift = -0.05 dB PMR not calibrated. PMF = 1.000 is applied. E-field emissions = 30.70 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-f	ield	
Grid 1 M4	Grid 2 M4	Grid 3 M4
26.67 V/m	28.65 V/m	28.15 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
19.03 V/m	30.70 V/m	30.76 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
27.41 V/m	38.06 V/m	38.05 V/m

Cursor:

Total = 38.06 V/m E Category: M4 Location: -8, 25, 8.7 mm

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_High_Chan/Hearing Aid

Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm Reference Value = 23.51 V/m; Power Drift = -0.00 dB PMR not calibrated. PMF = 1.000 is applied. E-field emissions = 33.39 V/m Near-field category: M4 (AWF 0 dB)

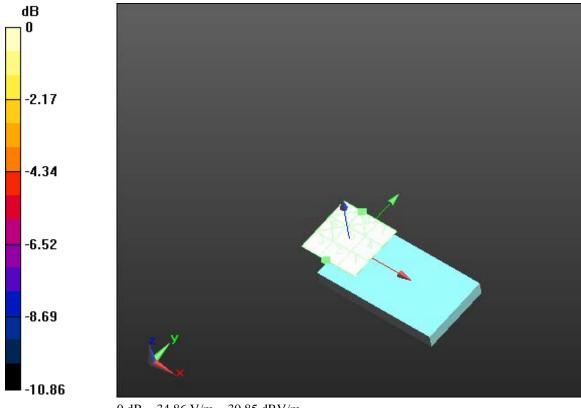
	ësting ervices:	Annex A to Hearing Aid Compatibility RF Emissions Test			Page 104 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

PMF scaled E-field	ld
--------------------	----

Grid 1 M4	Grid 2 M4	Grid 3 M4
31.58 V/m	33.39 V/m	32.54 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
19.34 V/m	26.91 V/m	27.30 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
25.79 V/m	37.66 V/m	37.66 V/m



Total = 37.66 V/m E Category: M4 Location: -8, 25, 8.7 mm



0 dB = 34.86 V/m = 30.85 dBV/m

	ting vices	Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW			Page 105 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARFI	M120LW

Date/Time: 4/4/2013 3:34:32 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_UMTS_Band_II_Telecoil

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 303E5577

Communication System: WCDMA FDD II; Frequency: 1907.6 MHz Medium parameters used: $\sigma = 0$ S/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

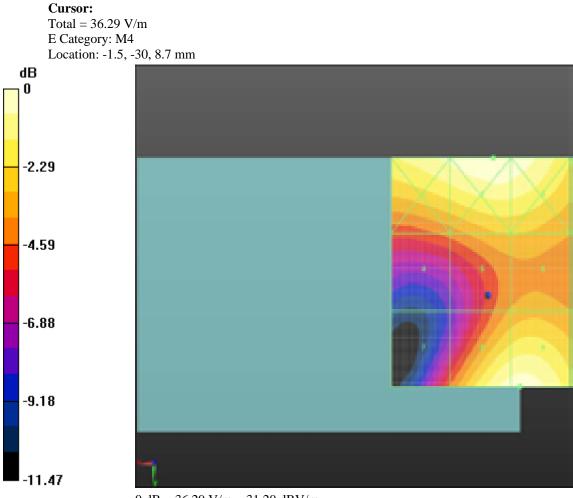
- Probe: ER3DV6 SN2286; ConvF(1, 1, 1); Calibrated: 1/11/2013;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_telecoil/Hearing Aid Compatibility Test (101x101x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mmDevice Reference Point: 0, 0, -6.3 mm Reference Value = 23.26 V/m; Power Drift = 0.07 dB PMR not calibrated. PMF = 1.000 is applied. E-field emissions = 35.23 V/m Near-field category: M4 (AWF 0 dB)

> PMF scaled E-field Grid 1 M4 Grid 2 **M4** Grid 3 **M4** 34.08 V/m 36.29 V/m 35.66 V/m Grid 4 **M4** Grid 5 **M4** Grid 6 **M4** 22.33 V/m 25.73 V/m 25.73 V/m Grid 7 **M4** Grid 8 **M4** Grid 9 **M4** 21.74 V/m 34.83 V/m 35.23 V/m

	esting arvices"	Annex A to Hearing Aid Compatibility RF Emissions Test			Page 106 (154)
Author Data Dates of Test Daoud Attayi Feb. 17-29, June 28, 2012			Report No RTS-6026-1304-09		M120LW
Daoud Attayi		7-29, June 20, 2012 03-04. 2013	RIS-6026-1304-09	LOAKF	



 $0 \ dB = 36.29 \ V/m = 31.20 \ dBV/m$

P#78	ting lices"	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW		Page 107 (154)	
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARFN	/120LW

Date/Time: 4/3/2013 4:55:51 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_CDMA850

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 303E5577

Communication System: CDMA 850, Communication System: CDMA 850 1/8th Rate; Frequency: 824.7 MHz, Frequency: 836.52 MHz, Frequency: 848.52 MHz Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 SN2286; ConvF(1, 1, 1); Calibrated: 1/11/2013;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to Device_Low_Chan_Full_Rate/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 71.27 V/m; Power Drift = -0.04 dB

PMR not calibrated. PMF = 1.060 is applied.

E-field emissions = 64.86 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-f	PMF scaled E-field						
Grid 1 M4	Grid 2 M4	Grid 3 M4					
53.92 V/m	62.40 V/m	62.36 V/m					
Grid 4 M4	Grid 5 M4	Grid 6 M4					
55.29 V/m	64.86 V/m	64.86 V/m					
Grid 7 M4	Grid 8 M4	Grid 9 M4					

	ting vices"	Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW		Page 108 (154)	
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi	Feb. 1	7-29, June 28, 2012	RTS-6026-1304-09	L6ARFI	M120LW
		03-04, 2013			

56.27 V/m 64.27 V/m 64.23 V/m

Cursor:

Total = 64.86 V/m E Category: M4 Location: -8.5, 4.5, 8.7 mm

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device Mid Chan Full Rate/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mmDevice Reference Point: 0, 0, -6.3 mm Reference Value = 73.04 V/m; Power Drift = -0.16 dB PMR not calibrated. PMF = 1.060 is applied.

E-field emissions = 67.52 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field Grid 2 **M4** Grid 3 **M4** Grid 1 **M4** 65.69 V/m 53.81 V/m 65.61 V/m Grid 4 **M4** Grid 5 **M4** Grid 6 M4 67.71 V/m 54.13 V/m 67.52 V/m Grid 7 **M4** Grid 8 **M4** Grid 9 M4 53.52 V/m 66.51 V/m 66.63 V/m

	ting vices		ompatibility RF Emissions T ® Smartphone model RFM12		Page 109 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARFI	M120LW

Cursor: Total = 67.71 V/m E Category: M4 Location: -9.5, 0.5, 8.7 mm

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the **Device High Chan Full Rate/Hearing Aid Compatibility Test**

(**101x101x1**): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 81.16 V/m; Power Drift = -0.04 dB

PMR not calibrated. PMF = 1.060 is applied.

E-field emissions = 76.00 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

	1010	
Grid 1 M4	Grid 2 M4	Grid 3 M4
62.54 V/m	74.66 V/m	74.66 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
60.89 V/m	76.00 V/m	76.04 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
58.67 V/m	74.18 V/m	74.20 V/m

Cursor:

Total = 76.04 V/m E Category: M4 Location: -9, 0, 8.7 mm

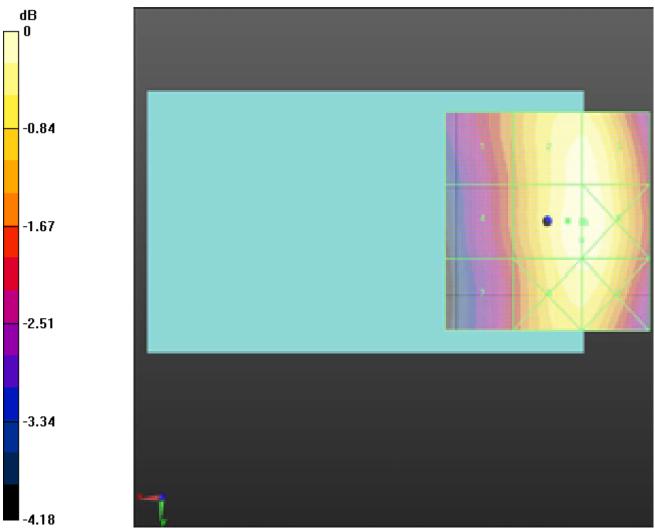
Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_High_Chan_1/8th_Rate/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 28.93 V/m; Power Drift = -0.03 dBPMR not calibrated. PMF = 2.900 is applied. E-field emissions = 83.19 V/m

Near-field category: M4 (AWF 0 dB)

	ésting ervices:		ompatibility RF Emissions T ® Smartphone model RFM12		Page 110 (154)
Author Data Daoud Attayi	Dates of T Feb. 1	^{est} 7-29, June 28, 2012	Report No RTS-6026-1304-09	FCC ID L6ARFI	M120LW
-	April	03-04. 2013			

PMF scaled E-fr	ield	
Grid 1 M4	Grid 2 $M4$	Grid 3 M4
67.57 V/m	77.76 V/m	79.08 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
59.94 V/m	83.19 V/m	81.99 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
62.77 V/m	79.52 V/m	81.55 V/m



0 dB = 64.86 V/m = 36.24 dBV/m

	isting rvices*		ompatibility RF Emissions 1 ® Smartphone model RFM12		Page 111 (154)
Author Data	Dates of T		Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

Date/Time: 4/3/2013 5:31:38 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_CDMA850_Telecoil

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 303E5577

Communication System: CDMA 850 1/8th Rate; Frequency: 848.52 MHz Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 SN2286; ConvF(1, 1, 1); Calibrated: 1/11/2013;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the_Device_High_Chan_1/8th_Rate_Telecoil/Hearing Aid

Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 29.67 V/m; Power Drift = -0.10 dB

.

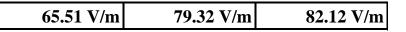
PMR not calibrated. PMF = 2.900 is applied.

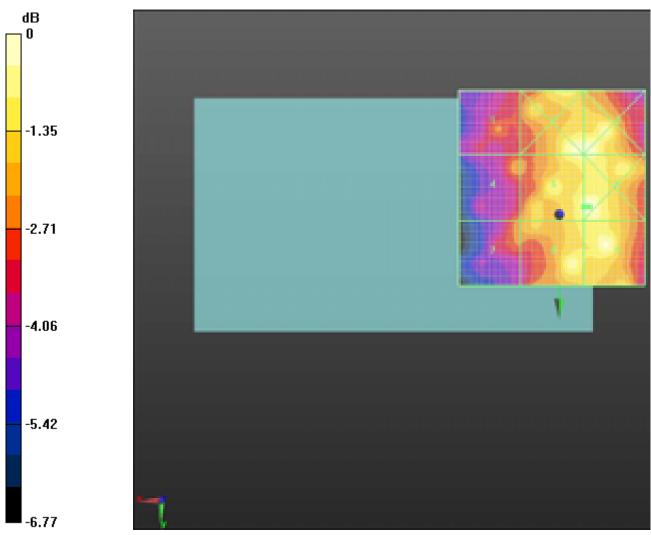
E-field emissions = 82.20 V/m

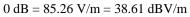
Near-field category: M4 (AWF 0 dB)

PMF scaled E-f	ïeld	
Grid 1 M4	Grid 2 M4	Grid 3 M4
63.22 V/m	82.44 V/m	83.11 V/m
Grid 4 M4	Grid 5 M4	Grid 6 ${f M4}$
65.71 V/m	82.20 V/m	85.26 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4

		Compatibility RF Emissions Te /® Smartphone model RFM12 ⁴		Page 112 (154)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	Feb. 17-29, June 28, 2012 April 03-04, 2013	RTS-6026-1304-09	L6ARFI	M120LW







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Author Data	Dates of T		Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARFN	/120LW

Date/Time: 4/3/2013 5:55:41 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_CDMA1900

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 303E5577

Communication System: CDMA 1900, Communication System: CDMA 1900 1/8th Rate; Frequency: 1851.25 MHz, Frequency: 1880 MHz, Frequency: 1908.5 MHz Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 SN2286; ConvF(1, 1, 1); Calibrated: 1/11/2013;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to Device_Low_Chan_Full_Rate/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 15.97 V/m; Power Drift = 0.27 dB

PMR not calibrated. PMF = 1.010 is applied.

E-field emissions = 26.17 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-f	ield	
Grid 1 ${f M4}$	Grid 2 M4	Grid 3 M4
24.55 V/m	26.17 V/m	26.00 V/m
Grid 4 M4	Grid 5 M4	Grid 6 ${f M4}$
17.88 V/m	24.34 V/m	24.42 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4

	ing ices		ompatibility RF Emissions Te not solve solve solve set to the set of the set		Page 114 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi	Feb. 1	7-29, June 28, 2012	RTS-6026-1304-09	L6ARF	M120LW
		03-04, 2013			

29.98 V/m 36.60 V/m 36.22 V/m

Cursor: Total = 36.60 V/m E Category: M4

Location: -6, 25, 8.7 mm

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device Mid Chan Full Rate/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mmDevice Reference Point: 0, 0, -6.3 mm Reference Value = 12.87 V/m; Power Drift = 0.33 dB PMR not calibrated. PMF = 1.010 is applied.

E-field emissions = 28.23 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field Grid 3 **M4** Grid 1 **M4** Grid 2 **M4** 26.51 V/m 28.23 V/m 27.53 V/m Grid 5 **M4** Grid 4 **M4** Grid 6 M4 15.45 V/m 23.84 V/m 24.34 V/m Grid 7 **M4** Grid 8 M4 Grid 9 M4 30.02 V/m 39.20 V/m 39.00 V/m

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device_High_Chan_Full_Rate/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 11.38 V/m; Power Drift = -0.06 dB PMR not calibrated. PMF = 1.010 is applied. E-field emissions = 26.36 V/m Near-field category: M4 (AWF 0 dB)

	êsting ervices:		ompatibility RF Emissions T ® Smartphone model RFM12		Page 115 (154)
Author Data	Dates of T		Report No	FCC ID	
Daoud Attayi	Feb. 1	7-29, June 28, 2012	RTS-6026-1304-09	L6ARF	M120LW
	April (03-04, 2013			

PMF	scaled E-field
-----	----------------

Grid 1 M4	Grid 2 M4	Grid 3 M4
24.77 V/m	26.36 V/m	26.03 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
13.35 V/m	20.56 V/m	21.03 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
27.54 V/m	35.07 V/m	34.77 V/m

Cursor:

Total = 35.07 V/m E Category: M4 Location: -6, 25, 8.7 mm

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_Mid_Chan_1/8th_Rate/Hearing Aid Compatibility Test

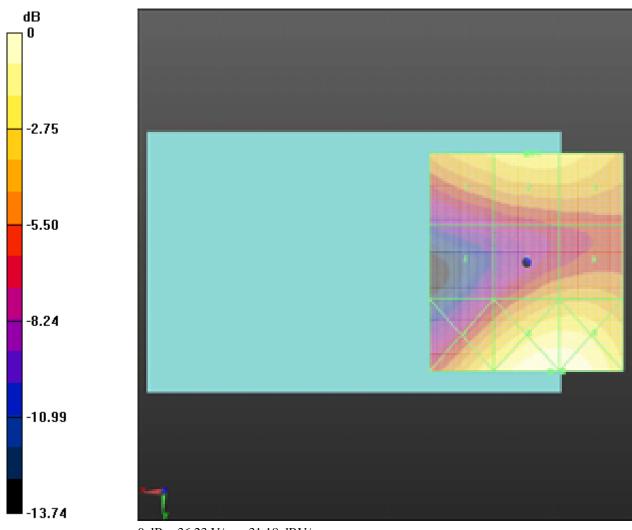
(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 4.858 V/m; Power Drift = -0.35 dB PMR not calibrated. PMF = 2.670 is applied. E-field emissions = 28.19 V/m

Near-field category: M4 (AWF 0 dB)

T WIT Scaled E-1	leid	
Grid 1 M4	Grid 2 M4	Grid 3 M4
24.55 V/m	28.19 V/m	25.60 V/m
Grid 4 M4	Grid 5 M4	Grid 6 ${f M4}$
14.53 V/m	24.38 V/m	25.99 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
27.19 V/m	39.17 V/m	39.67 V/m

PMF scaled E-field

	ting NCES"	Document Annex A to Hearing Aid Com Report for the BlackBerry® S			Page 116 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARFI	M120LW



 $0 \; dB = 36.23 \; V/m = 31.18 \; dBV/m$

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Author Data	Dates of T		Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARFN	/120LW

Date/Time: 4/3/2013 6:52:47 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_CDMA1900_Telecoil

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 303E5577

Communication System: CDMA 1900 1/8th Rate; Frequency: 1880 MHz Medium parameters used: $\sigma = 0$ S/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

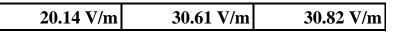
DASY Configuration:

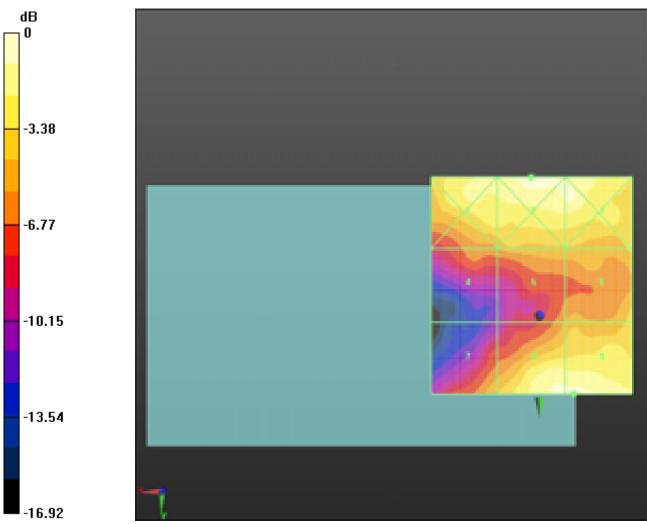
- Probe: ER3DV6 SN2286; ConvF(1, 1, 1); Calibrated: 1/11/2013;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the_Device_Mid_Chan_1/8th_Rate_Telecoil/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 4.649 V/m; Power Drift = -0.12 dB PMR not calibrated. PMF = 2.670 is applied. E-field emissions = 30.82 V/m **Near-field category: M4 (AWF 0 dB)**

PMF scaled E-f	ield	
Grid 1 M4	Grid 2 M4	Grid 3 M4
28.03 V/m	33.53 V/m	30.41 V/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
17.34 V/m	19.59 V/m	21.52 V/m
Grid 7 M4	Grid 8 M4	Grid 9 M4

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Author Data	Dates of T	est	Report No	FCC ID	
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0 dB = 33.53 V/m = 30.51 dBV/m

	ting vices		ompatibility RF Emissions T ® Smartphone model RFM12		Page 119 (154)
Author Data	Dates of T		Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

Date/Time: 4/4/2013 4:57:29 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_GSM_850

DUT: BlackBerry Smartphone; Type: Sample; Serial: 303E5577

Communication System: GSM 850; Frequency: 824.2 MHz, Frequency: 836.8 MHz, Frequency: 848.8 MHz Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field meausrement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_low_chan/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.04500 A/m; Power Drift = -0.05 dB

PMR not calibrated. PMF = 2.890 is applied.

H-field emissions = 0.2785 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-f	ïeld	
Grid 1 M4	Grid 2 M4	Grid 3 M4
0.279 A/m	0.198 A/m	0.133 A/m
Grid 4 M4	Grid 5 M4	Grid 6 ${f M4}$
0.235 A/m	0.170 A/m	0.111 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4

	esting arvices		ompatibility RF Emissions T ® Smartphone model RFM12		Page 120 (154)
Author Data Daoud Attayi		est 17-29, June 28, 2012 03-04, 2013	Report No RTS-6026-1304-09	FCC ID L6ARFI	M120LW

0.218 A/m 0.156 A/m 0.095 A/m

Device H-Field meausrement with H3DV6 probe/H Scan - H3DV6 -2007: 15 mm from Probe Center to the Device_mid_chan/Hearing

Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000

mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 0.04600 A/m; Power Drift = -0.08 dB PMR not calibrated. PMF = 2.890 is applied. H-field emissions = 0.2667 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.267 A/m Grid 4 M4	0.199 A/m Grid 5 M4	0.139 A/m Grid 6 M4
0.227 A/m	0.170 A/m	0.116 A/m
Grid 7 M4	Grid 8 M4	Grid 9 ${f M4}$
0.217 A/m	0.159 A/m	0.097 A/m

Device H-Field meausrement with H3DV6 probe/H Scan - H3DV6 -2007: 15 mm from Probe Center to the Device_high_chan/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000

mm

Device Reference Point: 0, 0, -6.3 mm Reference Value = 0.05500 A/m; Power Drift = -0.18 dB PMR not calibrated. PMF = 2.890 is applied. H-field emissions = 0.2981 A/m

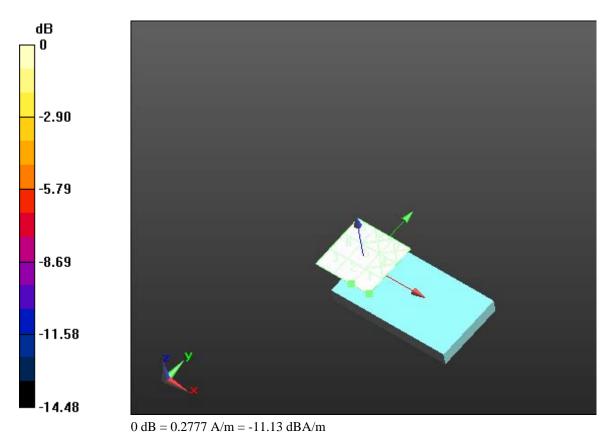
Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.298 A/m	0.224 A/m	0.153 A/m

	ting NCES"	Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW		Page 121 (154)	
Author Data	Dates of T		Report No	FCC ID	
Daoud Attayi	Feb. 1	7-29, June 28, 2012	RTS-6026-1304-09	L6ARF	M120LW
	April (03-04, 2013			

Grid 4 M4	Grid 5 M4	Grid 6 M4
0.257 A/m	0.196 A/m	0.132 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.253 A/m	0.192 A/m	0.126 A/m



	sting vices		ompatibility RF Emissions T		Page 122 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

Date/Time: 4/4/2013 5:08:10 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_GSM_850-Telecoil

DUT: BlackBerry Smartphone; Type: Sample; Serial: 303E5577

Communication System: GSM 850; Frequency: 848.8 MHz Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field meausrement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_telecoil/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.05400 A/m; Power Drift = 0.05 dB

PMR not calibrated. PMF = 2.890 is applied.

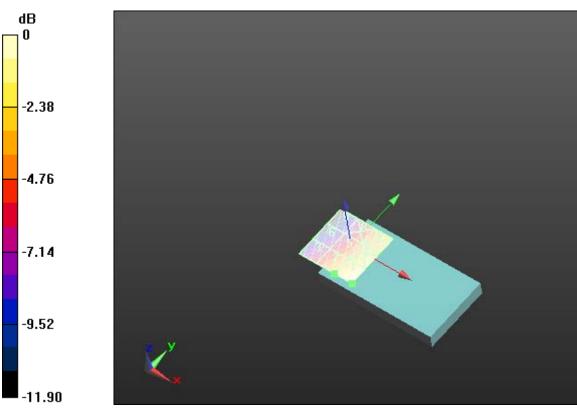
H-field emissions = 0.3164 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-f	ïeld	
Grid 1 M4	Grid 2 M4	Grid 3 M4
0.316 A/m	0.242 A/m	0.169 A/m
Grid 4 M4	Grid 5 M4	Grid 6 ${f M4}$
0.276 A/m	0.212 A/m	0.148 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4

Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW		Page 123 (154)			
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012)3-04, 2013	RTS-6026-1304-09	L6ARFI	M120LW

0.248 A/m 0.193 A/m 0.131 A/m



0 dB = 0.3154 A/m = -10.02 dBA/m

	ting vices		ompatibility RF Emissions T		Page 124 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARFI	M120LW

Date/Time: 4/4/2013 5:15:54 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_UMTS_Band_V

DUT: BlackBerry Smartphone; Type: Sample; Serial: 303E5577

Communication System: WCDMA FDD V; Frequency: 826.4 MHz, Frequency: 836.4 MHz, Frequency: 846.6 MHz Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field meausrement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_low_chan/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.05300 A/m; Power Drift = -0.06 dB

PMR not calibrated. PMF = 1.090 is applied.

H-field emissions = 0.1184 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-f	ïeld	
Grid 1 M4	Grid 2 $\mathbf{M4}$	Grid 3 ${f M4}$
0.118 A/m	0.087 A/m	0.059 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.100 A/m	0.075 A/m	0.049 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4

	ting vices		ompatibility RF Emissions To ® Smartphone model RFM12		Page 125 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012)3-04, 2013	RTS-6026-1304-09	L6ARFI	M120LW

0.096 A/m 0.070 A/m 0.043 A/m

Cursor:

Total = 0.1184 A/m H Category: M4 Location: 25, -25, 8.7 mm

Device H-Field meausrement with H3DV6 probe/H Scan - H3DV6 -2007: 15 mm from Probe Center to the Device_mid_chan/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm Reference Value = 0.05500 A/m; Power Drift = 0.05 dB PMR not calibrated. PMF = 1.090 is applied. H-field emissions = 0.1207 A/m

Near-field category: M4 (AWF 0 dB)

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.121 A/m	0.090 A/m	0.064 A/m
Grid 4 M4	Grid 5 M4	Grid 6 ${f M4}$
0.102 A/m	0.076 A/m	0.053 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.096 A/m	0.070 A/m	0.044 A/m

PMF scaled H-field

	esting ervices		ompatibility RF Emissions T		Page 126 (154)
Author Data	Dates of T		Report No	FCC ID	
Daoud Attayi	Feb. 1	7-29, June 28, 2012	RTS-6026-1304-09	L6ARF	M120LW
	April	03-04, 2013			

Cursor: Total = 0.1207 A/m H Category: M4 Location: 25, -25, 8.7 mm

Device H-Field meausrement with H3DV6 probe/H Scan - H3DV6 -2007: 15 mm from Probe Center to the Device_high_chan/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm Reference Value = 0.05600 A/m; Power Drift = 0.12 dBPMR not calibrated. PMF = 1.090 is applied. H-field emissions = 0.1154 A/m

Near-field category: M4 (AWF 0 dB)

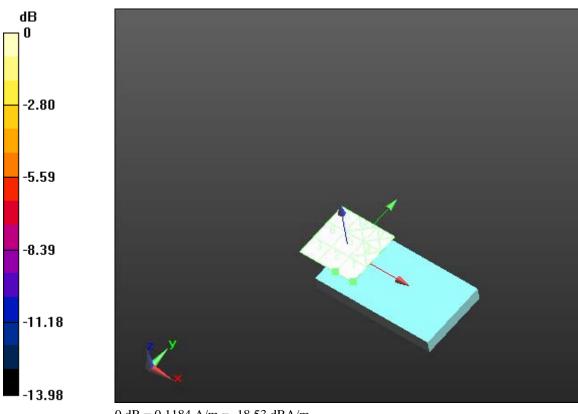
PMF scaled H-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.115 A/m	0.089 A/m	0.060 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.100 A/m	0.079 A/m	0.053 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.100 A/m	0.077 A/m	0.050 A/m

Cursor:

Total = 0.1154 A/m H Category: M4 Location: 25, -25, 8.7 mm

Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW		Page 127 (154)			
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW



0 dB = 0.1184 A/m = -18.53 dBA/m

	ting vices		ompatibility RF Emissions T ® Smartphone model RFM12		Page 128 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

Date/Time: 4/4/2013 5:22:57 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_UMTS_Band_V_Telecoil

DUT: BlackBerry Smartphone; Type: Sample; Serial: 303E5577

Communication System: WCDMA FDD V; Frequency: 836.4 MHz Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field meausrement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_telecoil/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.05500 A/m; Power Drift = 0.01 dB

PMR not calibrated. PMF = 1.090 is applied.

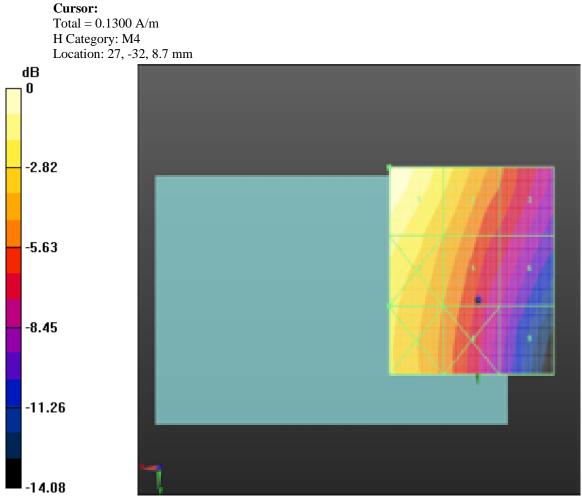
H-field emissions = 0.1300 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-f	ield	
Grid 1 M4	Grid 2 M4	Grid 3 M4
0.130 A/m	0.100 A/m	0.070 A/m
Grid 4 M4	Grid 5 M4	Grid 6 ${f M4}$
0.110 A/m	0.085 A/m	0.060 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4

	ting NCES"	Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW		Page 129 (154)	
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARFI	M120LW

0.099 A/m 0.076 A/m 0.050 A/m



 $0 \ dB = 0.1300 \ A/m = -17.72 \ dBA/m$

	ting vices		ompatibility RF Emissions T B Smartphone model RFM12		Page 130 (154)
Author Data	Dates of T		Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARFI	M120LW

Date/Time: 4/4/2013 4:42:51 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_GSM_1900

DUT: BlackBerry Smartphone; Type: Sample; Serial: 303E5577

Communication System: GSM 1900; Frequency: 1850.2 MHz, Frequency: 1880 MHz, Frequency: 1909.8 MHz Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field meausrement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_low_chan/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.05000 A/m; Power Drift = 0.15 dB

PMR not calibrated. PMF = 2.860 is applied.

H-field emissions = 0.1844 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-f	ïeld	
Grid 1 M3	Grid 2 M3	Grid 3 M3
0.184 A/m	0.140 A/m	0.140 A/m
Grid 4 M4	Grid 5 M3	Grid 6 M3
0.129 A/m	0.141 A/m	0.141 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4

	ing ices		ompatibility RF Emissions T Smartphone model RFM12		Page 131 (154)
Author Data	Dates of Te		Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012)3-04, 2013	RTS-6026-1304-09	L6ARFI	W120LW

0.123 A/m	0.125 A/m	0.125 A/m
-----------	-----------	-----------

Cursor:

Total = 0.1844 A/m H Category: M3 Location: 25, -25, 8.7 mm

Device H-Field meausrement with H3DV6 probe/H Scan - H3DV6 -2007: 15 mm from Probe Center to the Device_mid_chan/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm Reference Value = 0.06200 A/m; Power Drift = 0.02 dB PMR not calibrated. PMF = 2.860 is applied. H-field emissions = 0.1797 A/m

Near-field category: M3 (AWF -5 dB)

Grid 1 M3	Grid 2 M3	Grid 3 M3
0.180 A/m	0.166 A/m	0.166 A/m
Grid 4 M3	Grid 5 M3	Grid 6 M3
0.151 A/m	0.166 A/m	0.166 A/m
Grid 7 M3	Grid 8 M3	Grid 9 M3
0.169 A/m	0.149 A/m	0.144 A/m

PMF scaled H-field

Device H-Field meausrement with H3DV6 probe/H Scan - H3DV6 -2007: 15 mm from Probe Center to the Device_high_chan/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000

mm

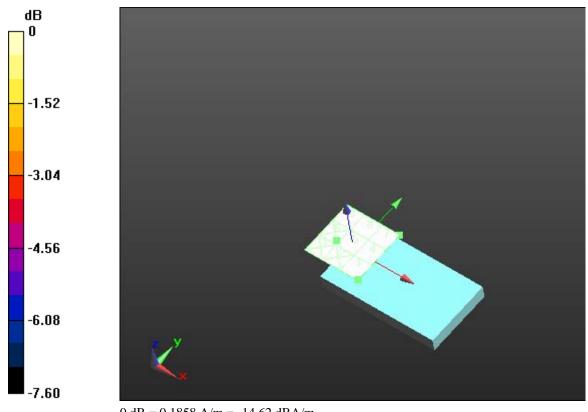
Device Reference Point: 0, 0, -6.3 mm Reference Value = 0.06900 A/m; Power Drift = 0.02 dBPMR not calibrated. PMF = 2.860 is applied. H-field emissions = 0.1959 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

	ting vices	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW		Page 132 (154)	
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARFI	M120LW

Grid 1 M3	Grid 2 M3	Grid 3 M3
0.196 A/m	0.192 A/m	0.193 A/m
Grid 4 M3	Grid 5 M3	Grid 6 M3
0.151 A/m	0.193 A/m	0.194 A/m
Grid 7 M3	Grid 8 M3	Grid 9 M3
0.182 A/m	0.179 A/m	0.179 A/m



0 dB = 0.1858 A/m = -14.62 dBA/m

	ting NCES"	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW		Page 133 (154)	
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

Date/Time: 4/4/2013 4:53:26 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_GSM_1900-Telecoil

DUT: BlackBerry Smartphone; Type: Sample; Serial: 303E5577

Communication System: GSM 1900; Frequency: 1909.8 MHz Medium parameters used: $\sigma = 0$ S/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field meausrement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_telecoil/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06900 A/m; Power Drift = 0.18 dB

PMR not calibrated. PMF = 2.860 is applied.

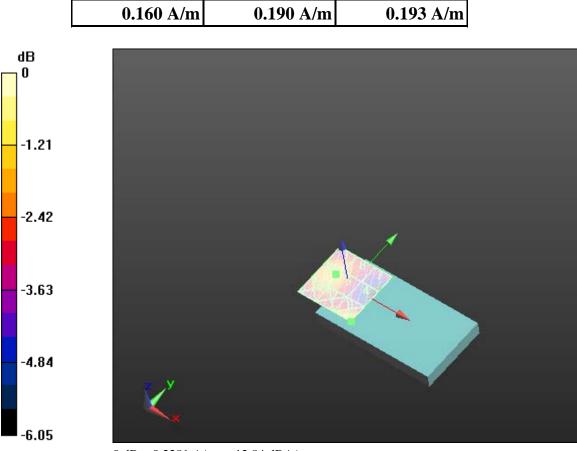
H-field emissions = 0.1965 A/m

Near-field category: M3 (AWF -5 dB)

I WII Scaled II-I	leia	
Grid 1 M3	Grid 2 M3	Grid 3 M3
0.226 A/m	0.185 A/m	0.188 A/m
Grid 4 M3	Grid 5 M3	Grid 6 M3
0.151 A/m	0.193 A/m	0.196 A/m
Grid 7 M3	Grid 8 M3	Grid 9 M3

PMF scaled H-field

P#78	ting vices		ompatibility RF Emissions Te ® Smartphone model RFM12 ²		Page 134 (154)
Author Data	Dates of T		Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012	RTS-6026-1304-09	L6ARFI	M120LW
	April	03-04, 2013			



0 dB = 0.2281 A/m = -12.84 dBA/m

Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW			Page 135 (154)		
Author Data	Dates of T		Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARFN	/120LW

Date/Time: 4/4/2013 1:24:24 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_GSM_1900_Telecoil_2100mA_Battery

DUT: BlackBerry Smartphone; Type: Sample; Serial: 303E5577

Communication System: GSM 1900; Frequency: 1909.8 MHz Medium parameters used: $\sigma = 0$ S/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

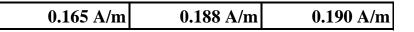
Device H-Field meausrement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device telecoil 2100mA Battery/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 0.07000 A/m; Power Drift = 0.02 dBPMR not calibrated. PMF = 2.860 is applied. H-field emissions = 0.1953 A/m

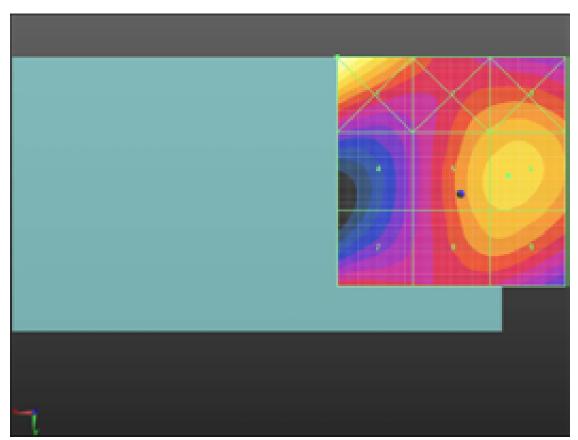
Near-field category: M3 (AWF -5 dB)

Fivit [®] scaled II-I	leiu	
Grid 1 M3	Grid 2 M3	Grid 3 M3
0.226 A/m	0.183 A/m	0.187 A/m
Grid 4 M3	Grid 5 M3	Grid 6 M3
0.150 A/m	0.192 A/m	0.195 A/m
Grid 7 M3	Grid 8 M3	Grid 9 M3

PMF scaled H-field

	ting NCES"	Annex A to Hearing Aid Compatibility RF Emissions Test		Page 136 (154)	
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARFI	M120LW





0 dB = 0.2272 A/m = -12.87 dBA/m

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Author Data	Dates of T		Report No	FCC ID	
Daoud Attayi Feb. 17-29, June 28, 2012		RTS-6026-1304-09	L6ARFN	/120LW	
	April	03-04, 2013			

Date/Time: 4/4/2013 5:52:03 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_UMTS_Band_II

DUT: BlackBerry Smartphone; Type: Sample; Serial: 303E5577

Communication System: WCDMA FDD II; Frequency: 1852.4 MHz, Frequency: 1880 MHz, Frequency: 1907.6 MHz Medium parameters used: $\sigma = 0$ S/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field meausrement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_low_chan/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08200 A/m; Power Drift = 0.08 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.09032 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-f	ïeld	
Grid 1 M4	Grid 2 M4	Grid 3 M4
0.090 A/m	0.079 A/m	0.079 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.071 A/m	0.079 A/m	0.079 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4

計響	Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW		Page 138 (154)		
Author Data Daoud Attayi		7-29, June 28, 2012	Report No RTS-6026-1304-09	FCC ID	W120LW
	April (03-04, 2013			

Cursor:

Total = 0.09032 A/m H Category: M4 Location: 25, -25, 8.7 mm

Device H-Field meausrement with H3DV6 probe/H Scan - H3DV6 -2007: 15 mm from Probe Center to the Device_mid_chan/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm Reference Value = 0.09200 A/m; Power Drift = 0.04 dB PMR not calibrated. PMF = 1.000 is applied. H-field emissions = 0.09346 A/m

Near-field category: M4 (AWF 0 dB)

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.093 A/m	0.087 A/m	0.086 A/m
Grid 4 ${f M4}$	Grid 5 M4	Grid 6 ${f M4}$
0.080 A/m	0.087 A/m	0.086 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.093 A/m	0.079 A/m	0.077 A/m

PMF scaled H-field

	esting ervices		ompatibility RF Emissions T		Page 139 (154)
Author Data	Dates of T		Report No	FCC ID	
Daoud Attayi	Feb. 1	7-29, June 28, 2012	RTS-6026-1304-09	L6ARF	M120LW
	April (03-04, 2013			

Cursor: Total = 0.09346 A/m H Category: M4 Location: 25, -25, 8.7 mm

Device H-Field meausrement with H3DV6 probe/H Scan - H3DV6 -2007: 15 mm from Probe Center to the Device_high_chan/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm Reference Value = 0.1020 A/m; Power Drift = 0.03 dBPMR not calibrated. PMF = 1.000 is applied. H-field emissions = 0.09856 A/m

Near-field category: M4 (AWF 0 dB)

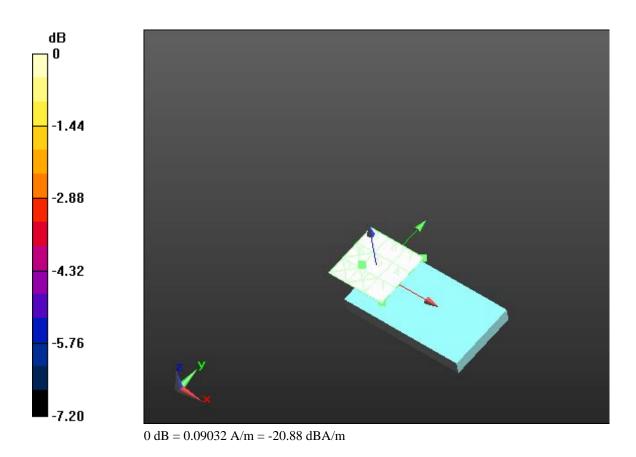
PMF scaled H-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.097 A/m	0.098 A/m	0.098 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.080 A/m	0.099 A/m	0.099 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.091 A/m	0.091 A/m	0.091 A/m

Cursor:

Total = 0.09871 A/m H Category: M4 Location: -10, -5.5, 8.7 mm

Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RFM121LW		Page 140 (154)			
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW



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	ting vices"		ompatibility RF Emissions Te Smartphone model RFM12		Page 141 (154)
Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARFI	M120LW

Date/Time: 4/4/2013 9:30:08 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_UMTS_Band_II_Telecoil

DUT: BlackBerry Smartphone; Type: Sample; Serial: 303E5577

Communication System: WCDMA FDD II; Frequency: 1907.6 MHz Medium parameters used: $\sigma = 0$ S/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field meausrement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_telecoil/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.09800 A/m; Power Drift = 0.04 dB

PMR not calibrated. PMF = 1.000 is applied.

H-field emissions = 0.1080 A/m

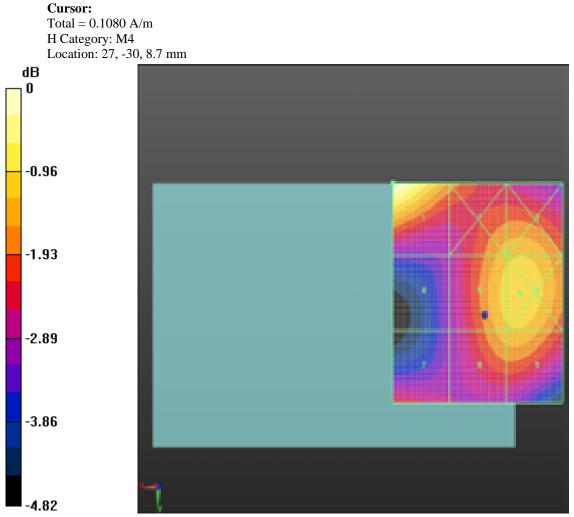
Near-field category: M4 (AWF 0 dB)

F WIF Scaled 11-1	leid	
Grid 1 M4	Grid 2 M4	Grid 3 M4
0.108 A/m	0.092 A/m	0.093 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.077 A/m	0.095 A/m	0.096 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4

PMF scaled H-field

	sting vices		ompatibility RF Emissions To s Smartphone model RFM12		Page 142 (154)
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0.083 A/m	0.092 A/m	0.093 A/m
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0 dB = 0.1080 A/m = -19.33 dBA/m

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Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARFN	/120LW

Date/Time: 4/4/2013 10:08:26 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_CDMA850

DUT: BlackBerry Smartphone; Type: Sample; Serial: 303E5577

Communication System: CDMA 850, Communication System: CDMA 850 1/8th Rate; Frequency: 824.7 MHz, Frequency: 836.52 MHz, Frequency: 848.52 MHz Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field meausrement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_low_chan_Full_Rate/Hearing Aid

Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07500 A/m; Power Drift = -0.03 dB

PMR not calibrated. PMF = 1.030 is applied.

H-field emissions = 0.1220 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-f	ïeld	
Grid 1 M4	Grid 2 M4	Grid 3 M4
0.122 A/m	0.090 A/m	0.058 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.130 A/m	0.097 A/m	0.066 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4

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0.154 A/m 0.113 A/m 0.078 A/m

Cursor:

Total = 0.1541 A/m H Category: M4 Location: 25, 25, 8.7 mm

Device H-Field meausrement with H3DV6 probe/H Scan - H3DV6 -2007: 15 mm from Probe Center to the Device mid chan Full Rate/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07100 A/m; Power Drift = 0.12 dB

PMR not calibrated. PMF = 1.030 is applied.

H-field emissions = 0.1225 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field Grid 2 **M4** Grid 3 **M4** Grid 1 **M4** 0.055 A/m 0.123 A/m 0.089 A/m Grid 4 **M4** Grid 5 **M4** Grid 6 M4 0.127 A/m 0.095 A/m 0.064 A/m Grid 7 **M4** Grid 8 **M4** Grid 9 **M4** 0.150 A/m 0.111 A/m 0.077 A/m

	esting ervices		ompatibility RF Emissions T ® Smartphone model RFM12		Page 145 (154)
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Cursor: Total = 0.1500 A/m H Category: M4 Location: 25, 25, 8.7 mm

Device H-Field meausrement with H3DV6 probe/H Scan - H3DV6 -2007: 15 mm from Probe Center to the Device high chan Full Rate/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mmDevice Reference Point: 0, 0, -6.3 mm Reference Value = 0.09500 A/m; Power Drift = -0.01 dB PMR not calibrated. PMF = 1.030 is applied. H-field emissions = 0.1434 A/m

Near-field category: M4 (AWF 0 dB)

T MIT Sealed IT I	ieia	
Grid 1 M4	Grid 2 M4	Grid 3 M4
0.143 A/m	0.111 A/m	0.076 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.153 A/m	0.121 A/m	0.089 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.180 A/m	0.141 A/m	0.105 A/m

PMF scaled H-field

Cursor:

Total = 0.1804 A/m H Category: M4 Location: 25, 25, 8.7 mm

Device H-Field meausrement with H3DV6 probe/H Scan - H3DV6 -2007: 15 mm from Probe Center to the Device_high_chan_1/8th_Rate/Hearing Aid Compatibility Test

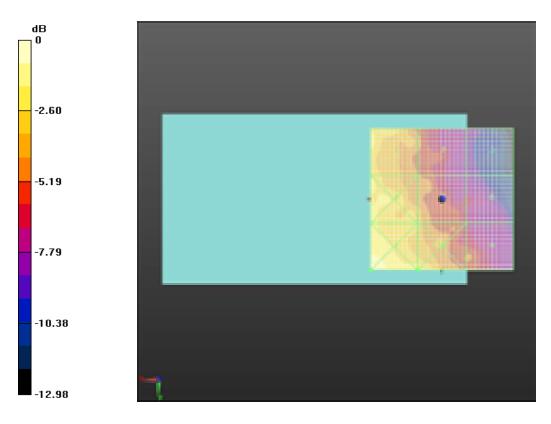
(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mmDevice Reference Point: 0, 0, -6.3 mm Reference Value = 0.03900 A/m; Power Drift = 0.08 dB PMR not calibrated. PMF = 2.650 is applied. H-field emissions = 0.1511 A/m Near-field category: M4 (AWF 0 dB)

	esting ervices"		ompatibility RF Emissions 1 ® Smartphone model RFM12		Page 146 (154)
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PMF	scaled	H-field
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Grid 1 M4	Grid 2 M4	Grid 3 M4
0.151 A/m	0.111 A/m	0.073 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.158 A/m	0.125 A/m	0.087 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.191 A/m	0.151 A/m	0.105 A/m

Cursor: Total = 0.1913 A/m H Category: M4 Location: 25, 25, 8.7 mm



0 dB = 0.1541 A/m = -16.24 dBA/m

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Author Data	Dates of T	est	Report No	FCC ID	
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARF	M120LW

Date/Time: 4/4/2013 11:58:51 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_CDMA850_Telecoil

DUT: BlackBerry Smartphone; Type: Sample; Serial: 303E5577

Communication System: CDMA 850 1/8th Rate; Frequency: 848.52 MHz Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field meausrement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_telecoil_1/8th Rate/Hearing Aid Compatibility

Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

.

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.03400 A/m; Power Drift = 0.27 dB

PMR not calibrated. PMF = 2.650 is applied.

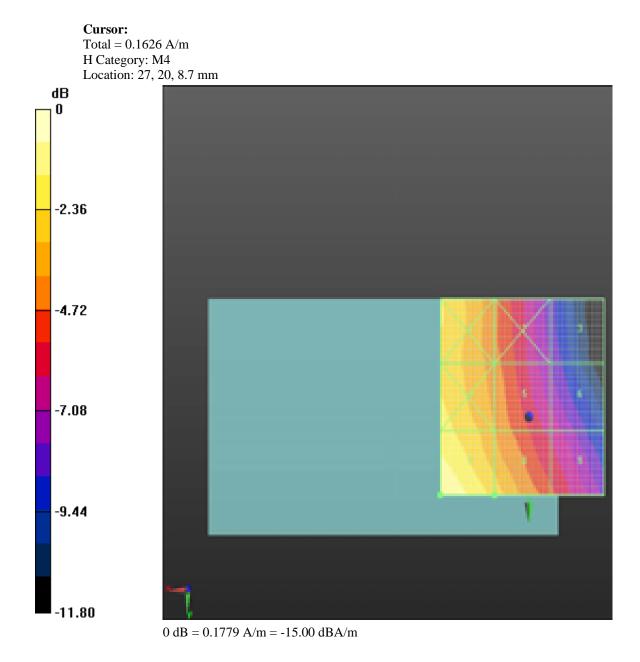
H-field emissions = 0.1626 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-f	ield	
Grid 1 M4	Grid 2 M4	Grid 3 M4
0.137 A/m	0.108 A/m	0.073 A/m
Grid 4 M4	Grid 5 M4	Grid 6 ${f M4}$
0.142 A/m	0.114 A/m	0.084 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4

	sting rvices		ompatibility RF Emissions T ® Smartphone model RFM12		Page 148 (154)
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0.163 A/m	0.131 A/m	0.098 A/m
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	esting arvices		ompatibility RF Emissions T ® Smartphone model RFM12		Page 149 (154)
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Date/Time: 4/4/2013 11:07:00 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_CDMA1900

DUT: BlackBerry Smartphone; Type: Sample; Serial: 303E5577

Communication System: CDMA 1900, Communication System: CDMA 1900 1/8th Rate; Frequency: 1851.25 MHz, Frequency: 1880 MHz, Frequency: 1908.5 MHz Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field meausrement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_low_chan_Full_Rate/Hearing Aid

Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08400 A/m; Power Drift = -0.13 dB

PMR not calibrated. PMF = 0.9900 is applied.

H-field emissions = 0.08507 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-f	ield	
Grid 1 M4	Grid 2 $\mathbf{M4}$	Grid 3 M4
0.059 A/m	0.083 A/m	0.084 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.062 A/m	0.084 A/m	0.085 A/m

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Grid 7 M4	Grid 8 M4	Grid 9 M4
0.086 A/m	0.080 A/m	0.080 A/m

Device H-Field meausrement with H3DV6 probe/H Scan - H3DV6 -2007: 15 mm from Probe Center to the Device mid abon Expl. Dete/Hearing Aid Compatibility Test

Device_mid_chan_Full_Rate/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mmDevice Reference Point: 0, 0, -6.3 mm Reference Value = 0.09100 A/m; Power Drift = 0.17 dB PMR not calibrated. PMF = 0.9900 is applied.

H-field emissions = 0.09190 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
0.065 A/m	0.089 A/m	0.089 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.071 A/m	0.091 A/m	0.092 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.096 A/m	0.088 A/m	0.088 A/m

Device H-Field meausrement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device_high_chan_Full_Rate/Hearing Aid Compatibility Test

(**101x101x1**): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08500 A/m; Power Drift = 0.19 dB

PMR not calibrated. PMF = 0.9900 is applied.

H-field emissions = 0.08743 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 M4 Grid 2 M4 Grid 3 M4
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	ting vices		ompatibility RF Emissions Te ® Smartphone model RFM12 ⁴		Page 151 (154)
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0.059 A/m	0.084 A/m	0.085 A/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
0.069 A/m	0.087 A/m	0.087 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.095 A/m	0.084 A/m	0.085 A/m

Device H-Field meausrement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device_mid_chan_1/8th_Rate/Hearing Aid Compatibility Test

(101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.03200 A/m; Power Drift = -0.09 dB

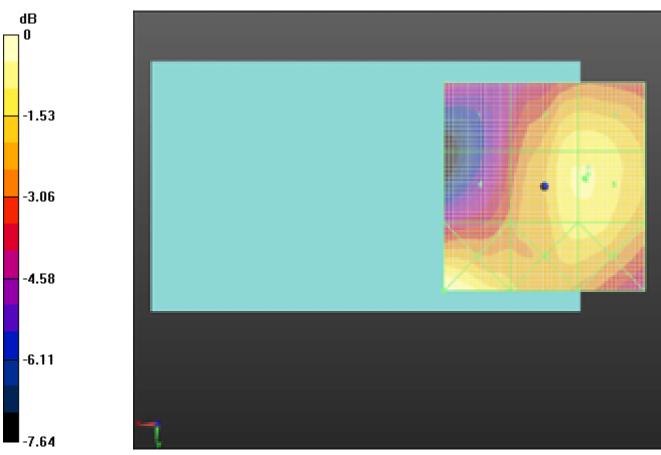
PMR not calibrated. PMF = 2.600 is applied.

H-field emissions = 0.08217 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-f	ïeld	
Grid 1 M4	Grid 2 M4	Grid 3 M4
0.059 A/m	0.080 A/m	0.080 A/m
Grid 4 M4	Grid 5 M4	Grid 6 ${f M4}$
0.065 A/m	0.082 A/m	0.082 A/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
0.090 A/m	0.080 A/m	0.080 A/m

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Author Data	Dates of T	est	Report No FCC ID		
Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARFI	M120LW



0 dB = 0.08624 A/m = -21.29 dBA/m

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Daoud Attayi		7-29, June 28, 2012 03-04, 2013	RTS-6026-1304-09	L6ARFN	/120LW

Date/Time: 4/4/2013 11:52:41 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_CDMA1900_Telecoil

DUT: BlackBerry Smartphone; Type: Sample; Serial: 303E5577

Communication System: CDMA 1900; Frequency: 1880 MHz Medium parameters used: $\sigma = 0$ S/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn881; Calibrated: 1/14/2013
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field meausrement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_telecoil_Full_Rate/Hearing Aid Compatibility

Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.09200 A/m; Power Drift = -0.00 dB

PMR not calibrated. PMF = 0.9900 is applied.

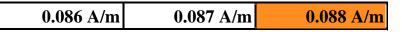
H-field emissions = 0.08692 A/m

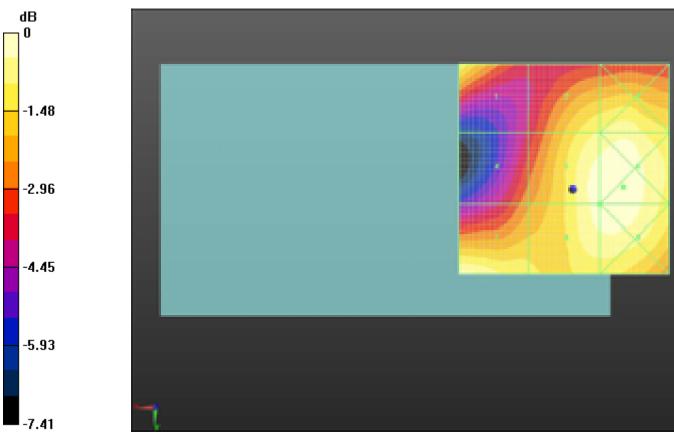
Near-field category: M4 (AWF 0 dB)

_	PMF scaled H-I	leid	
	Grid 1 ${f M4}$	Grid 2 M4	Grid 3 M4
	0.080 A/m	0.080 A/m	0.083 A/m
	Grid 4 M4	Grid 5 M4	Grid 6 M4
	0.066 A/m	0.087 A/m	0.089 A/m
	Grid 7 ${f M4}$	Grid 8 M4	Grid 9 M4

DME scaled H field

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0 dB = 0.08924 A/m = -20.99 dBA/m